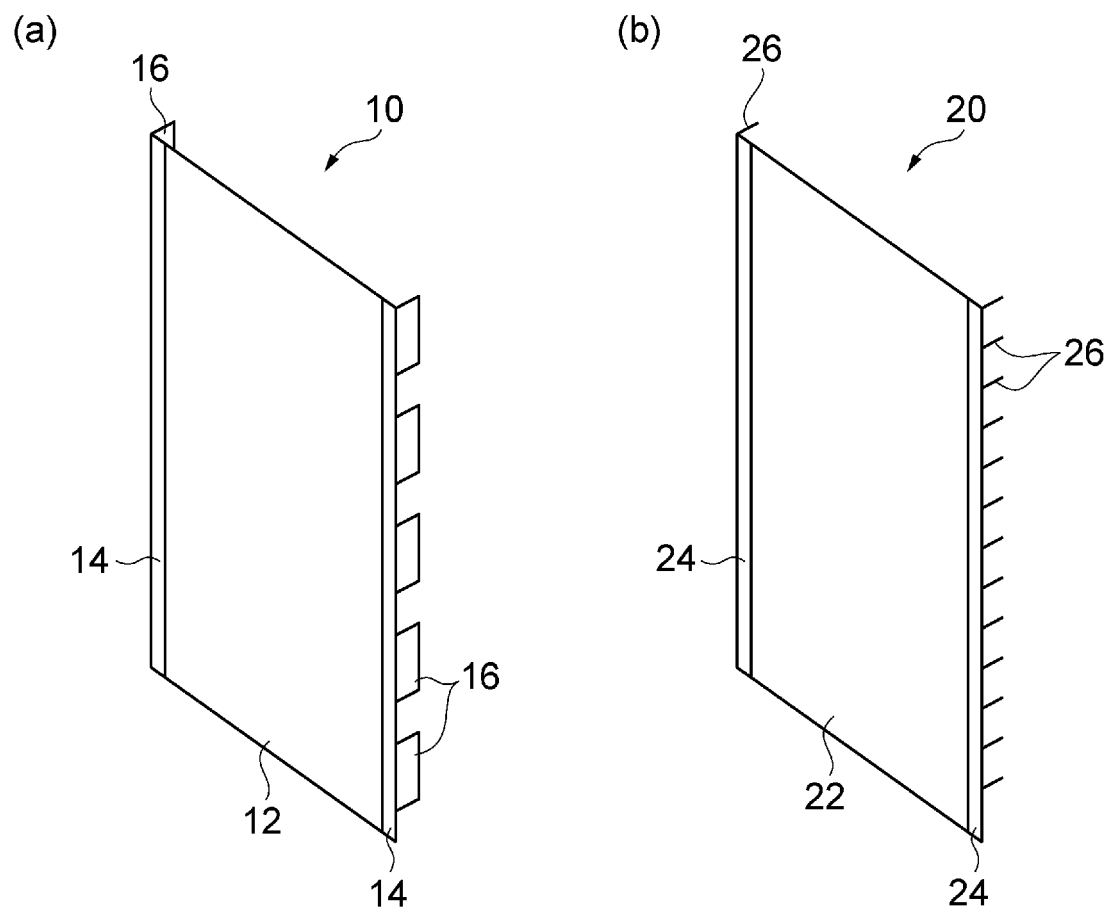
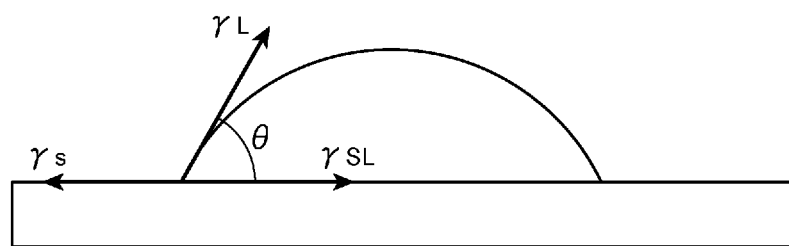


[図1]

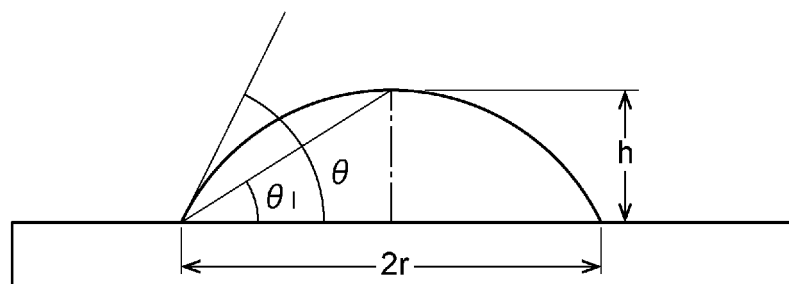


[図2]

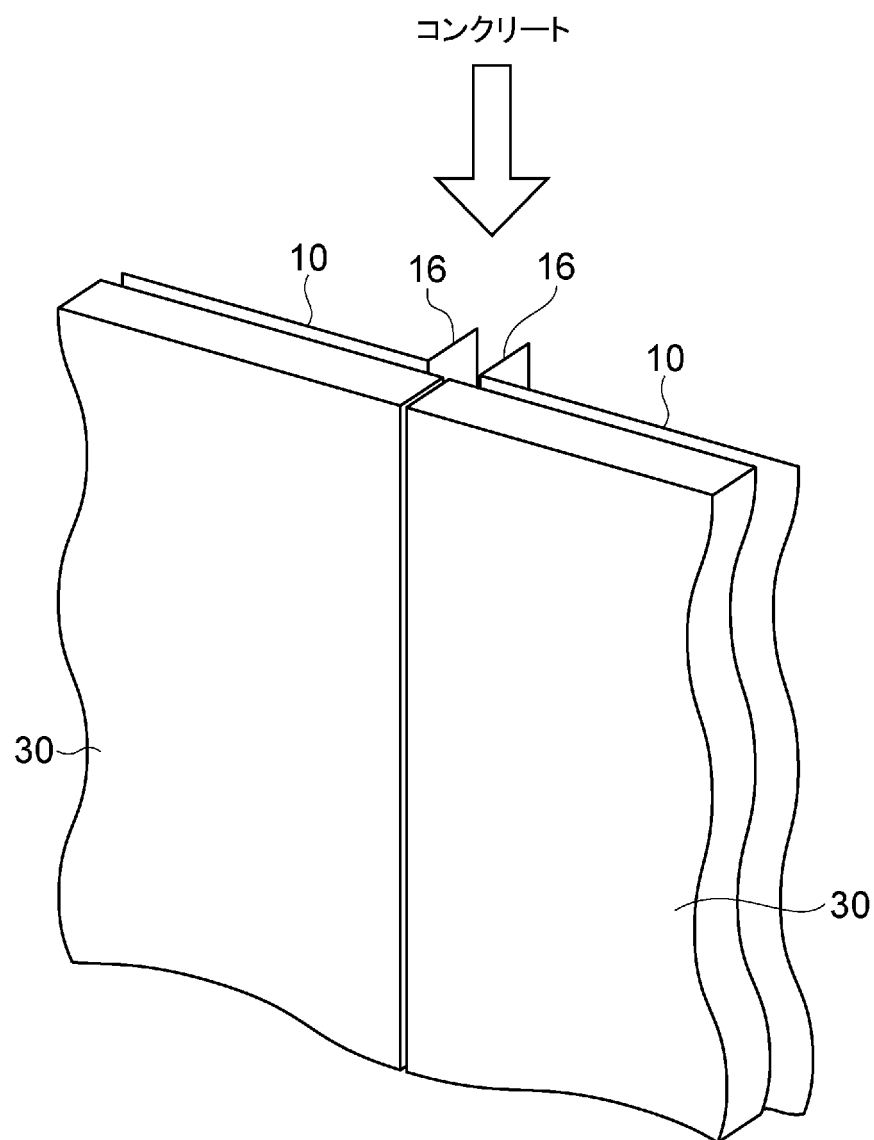
(a)



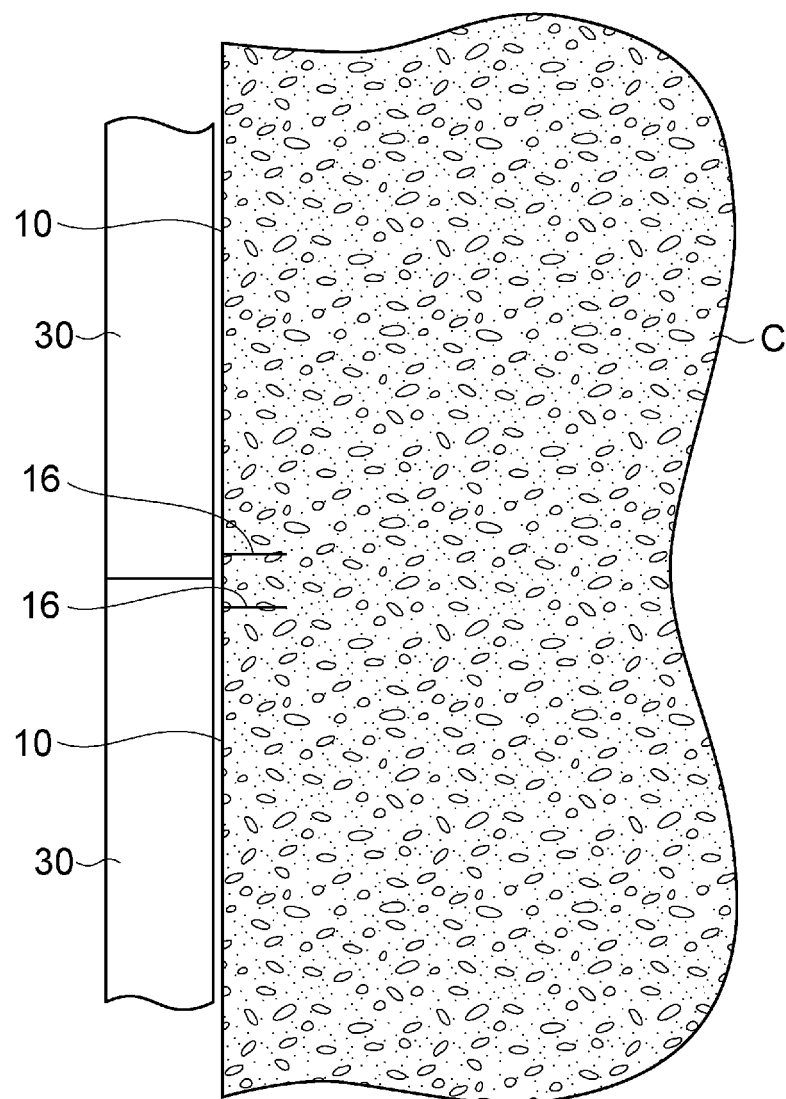
(b)



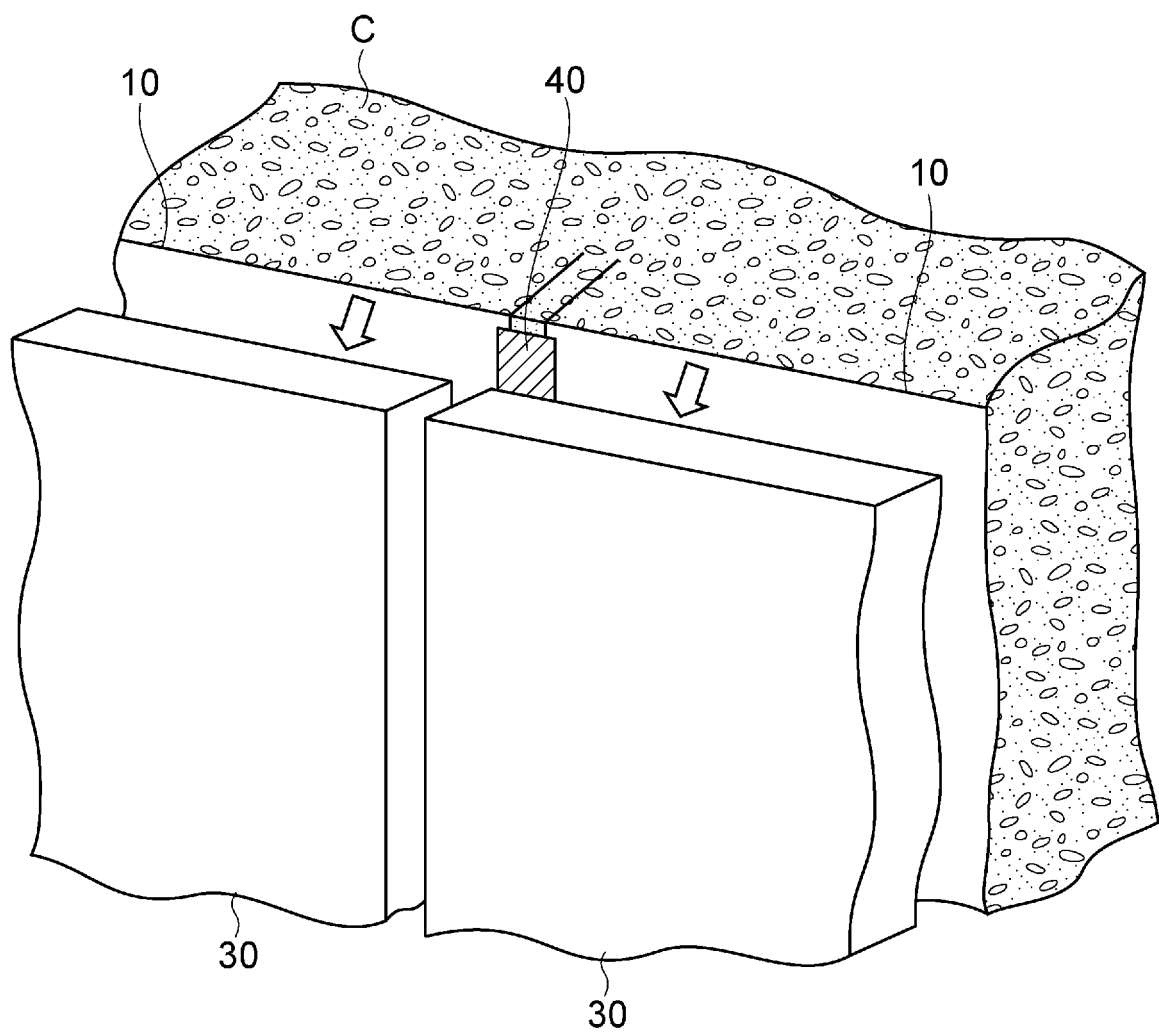
[図3]



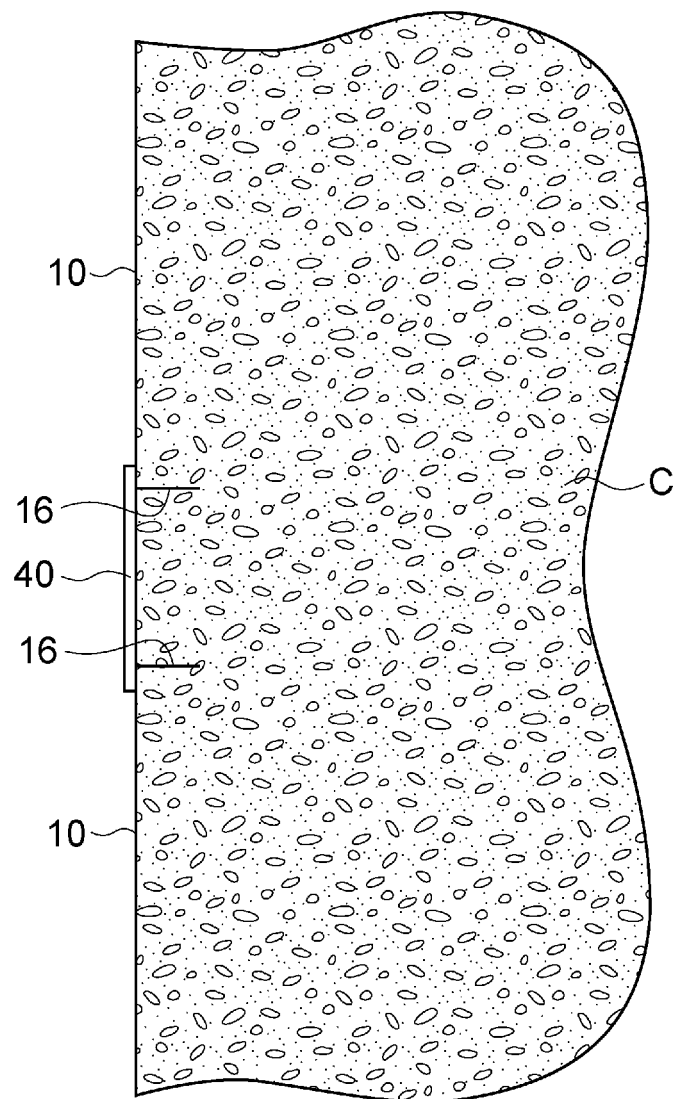
[図4]



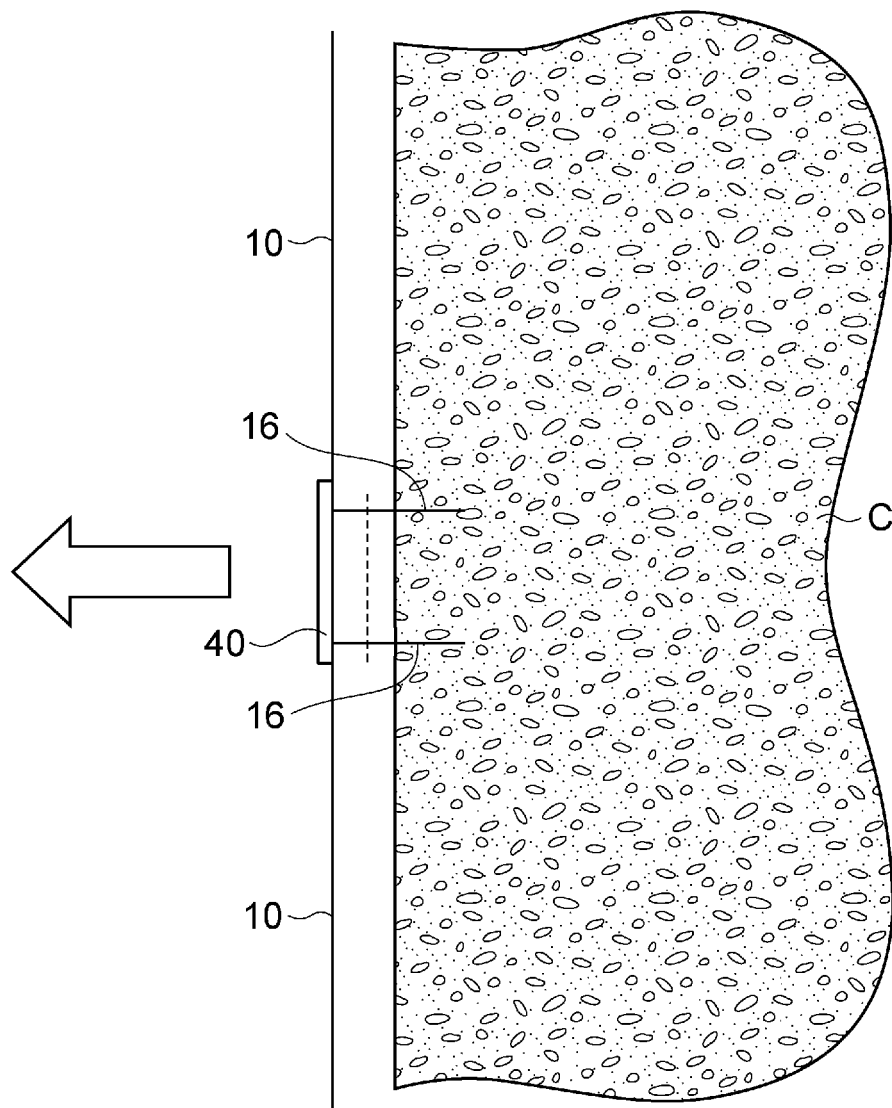
[図5]



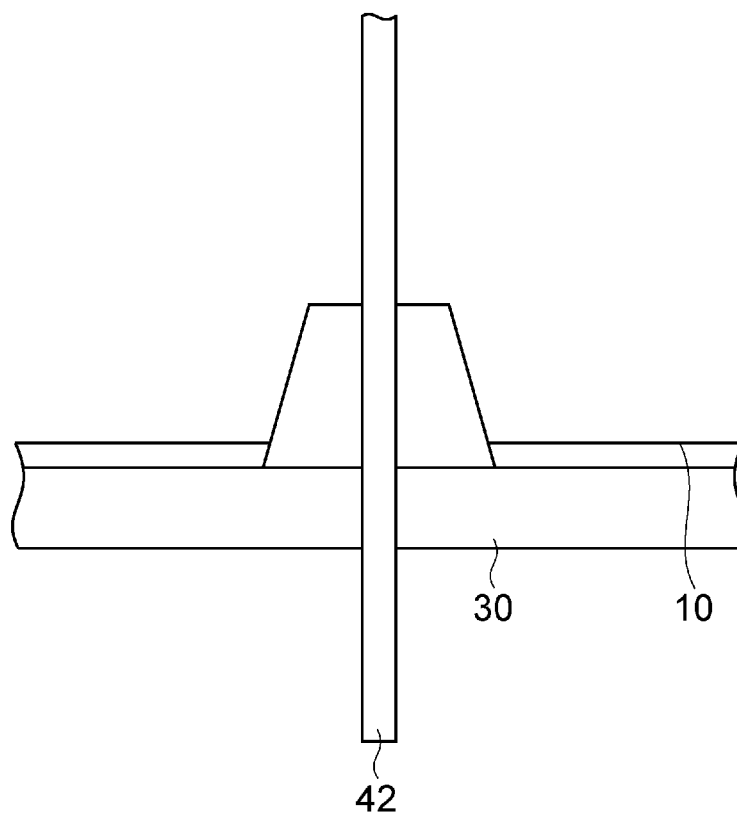
[図6]



[図7]

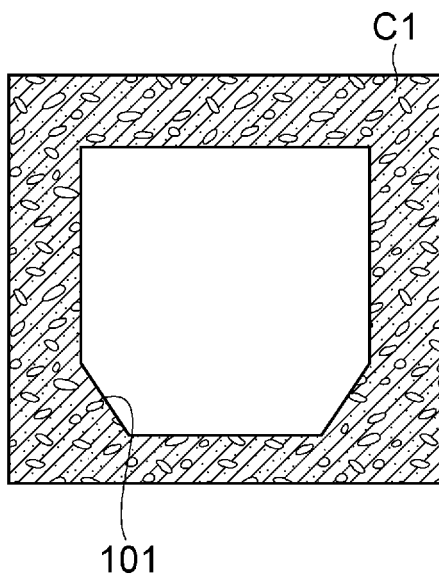


[図8]

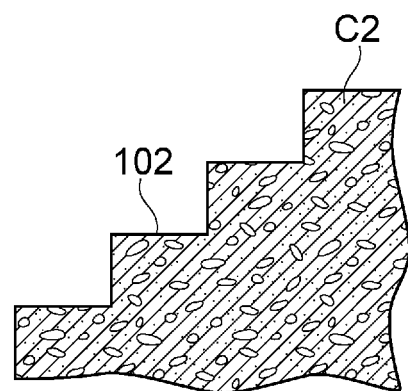


[図9]

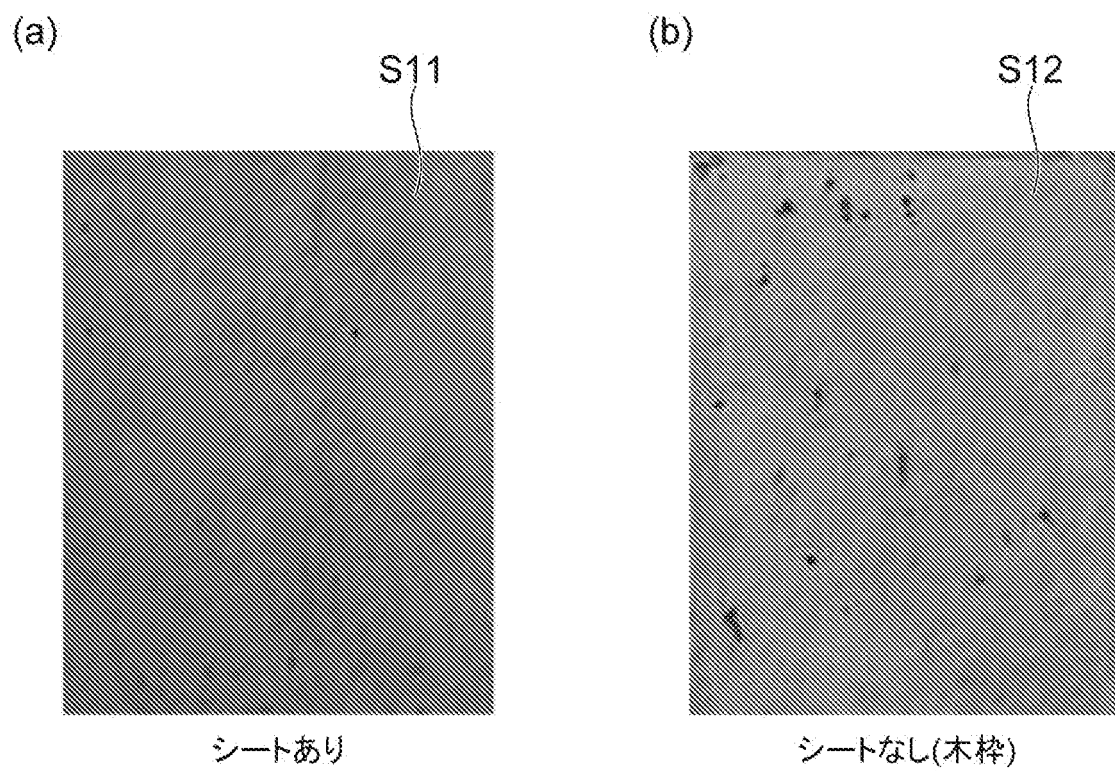
(a)



(b)

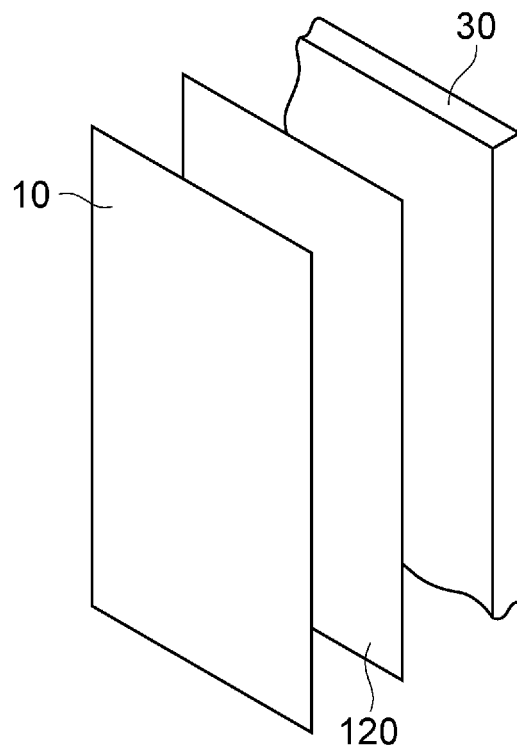


[図10]

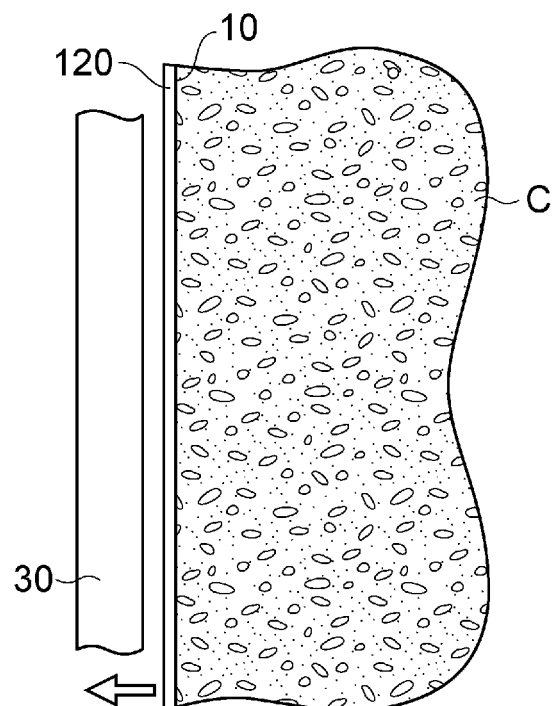


[図11]

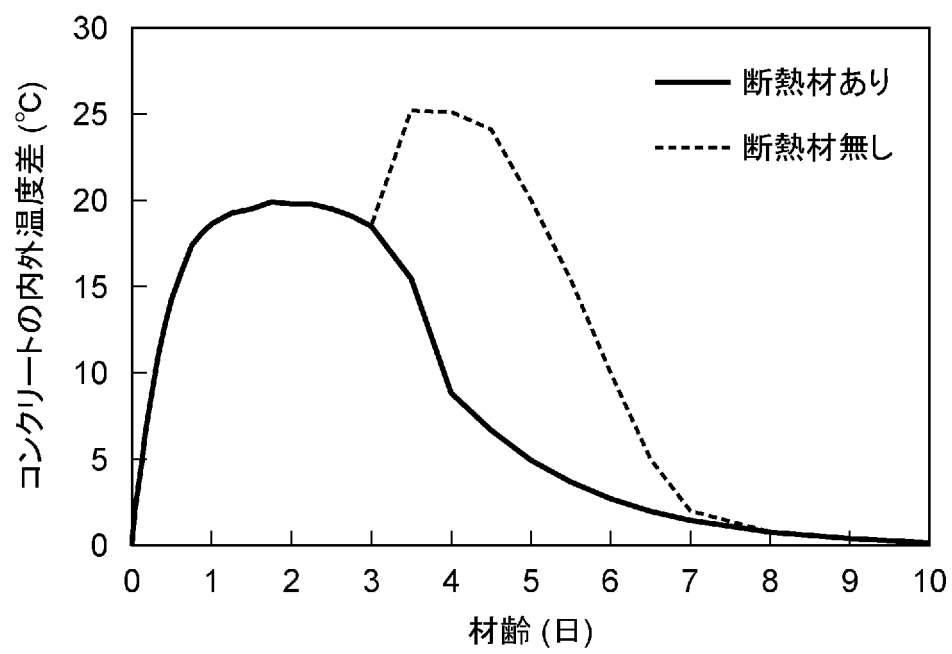
(a)



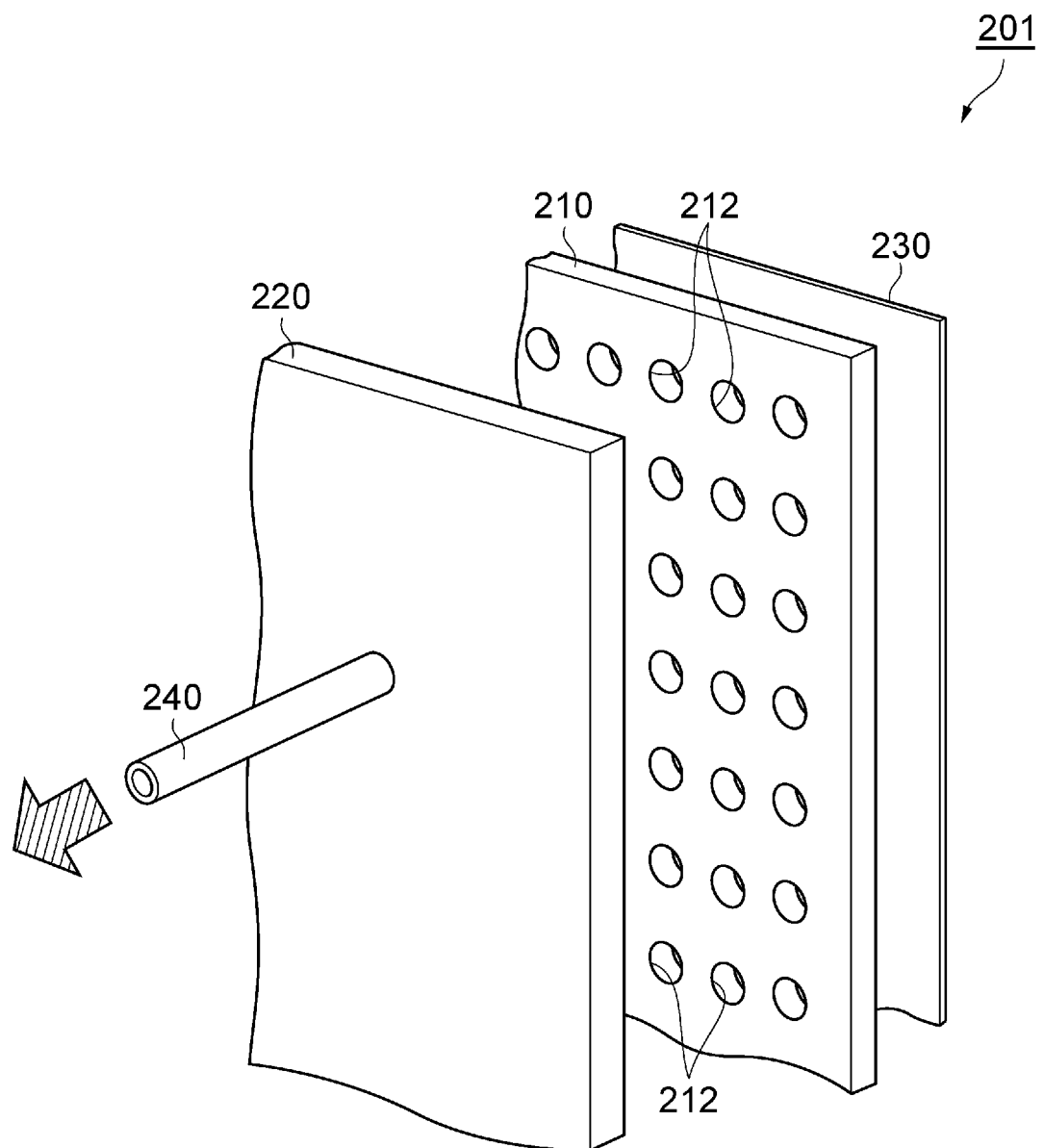
(b)



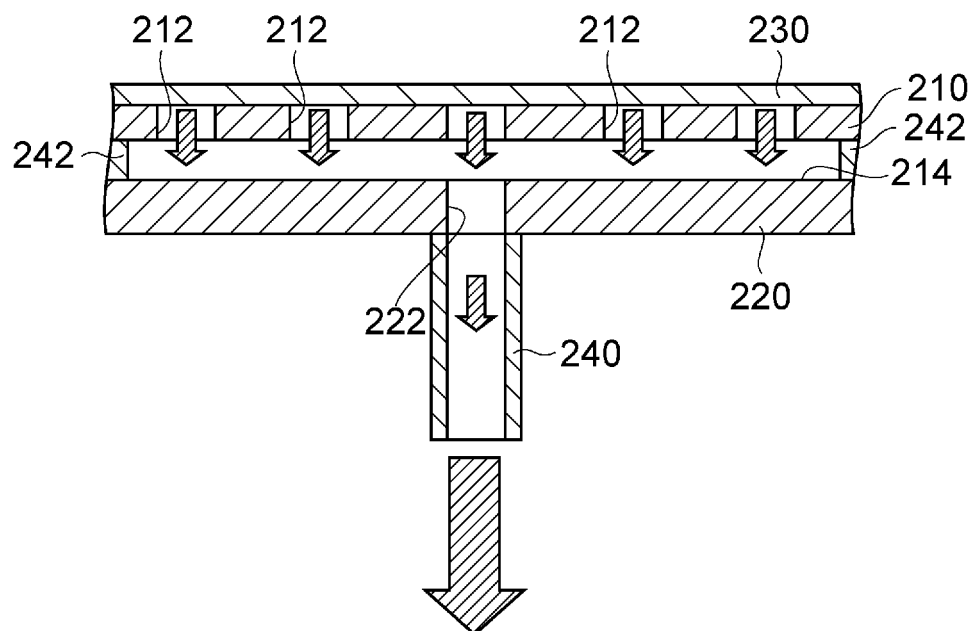
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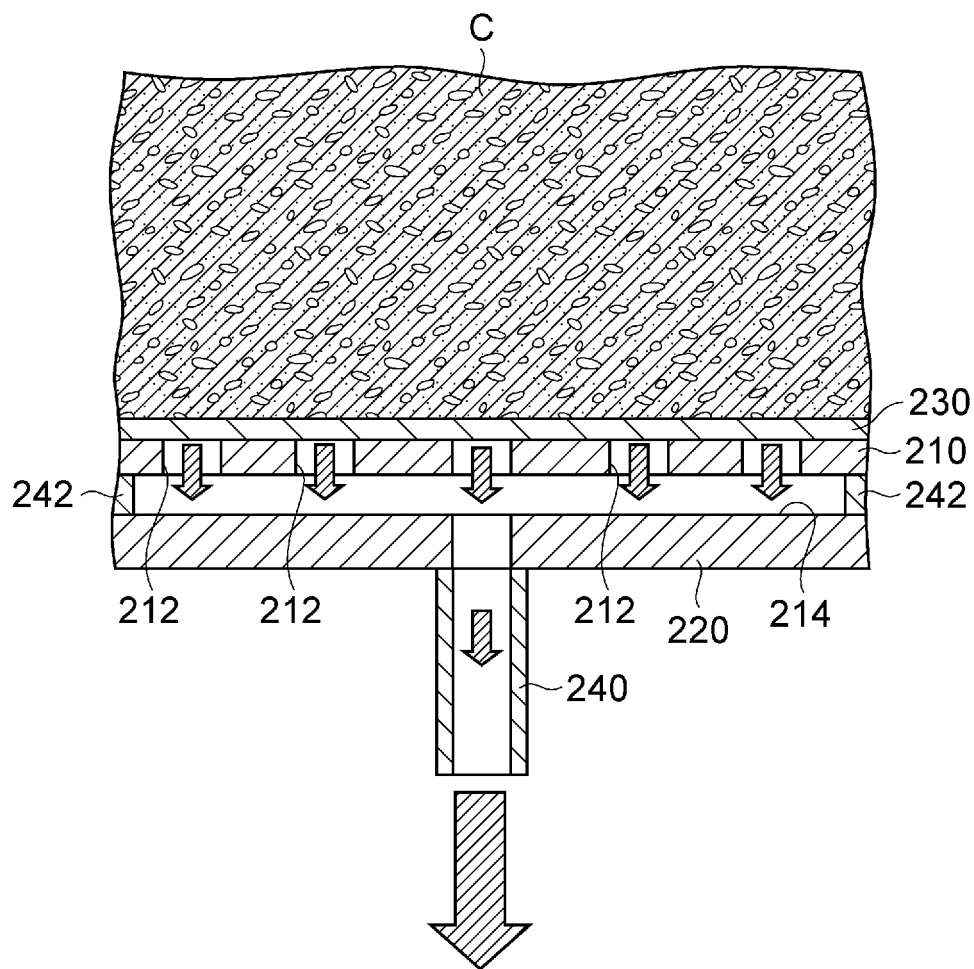
[図13]



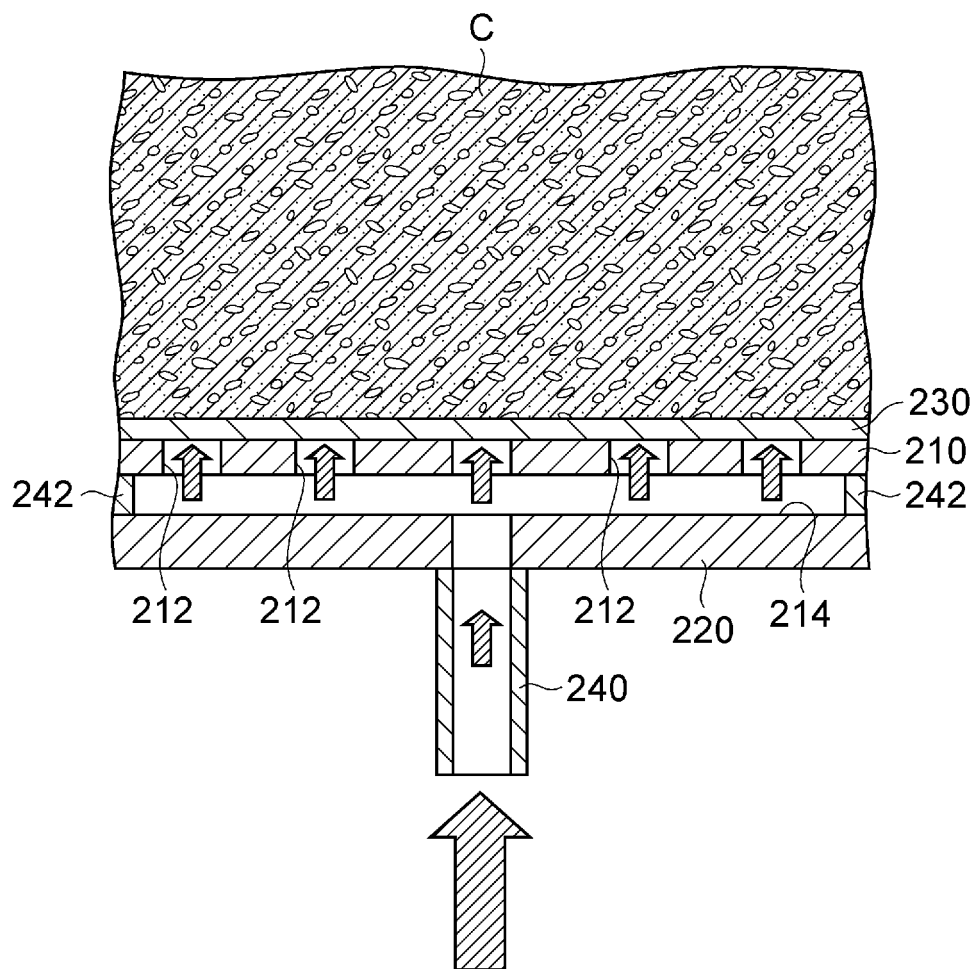
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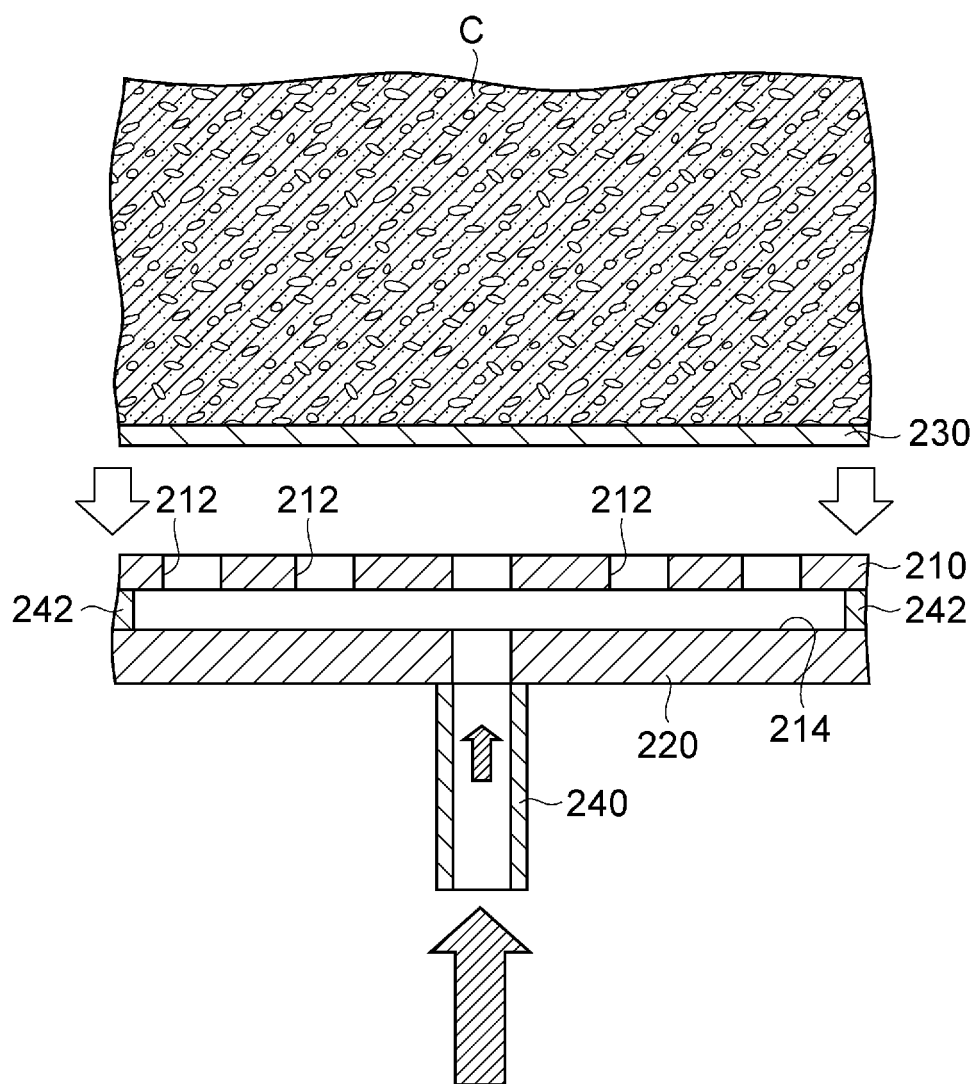
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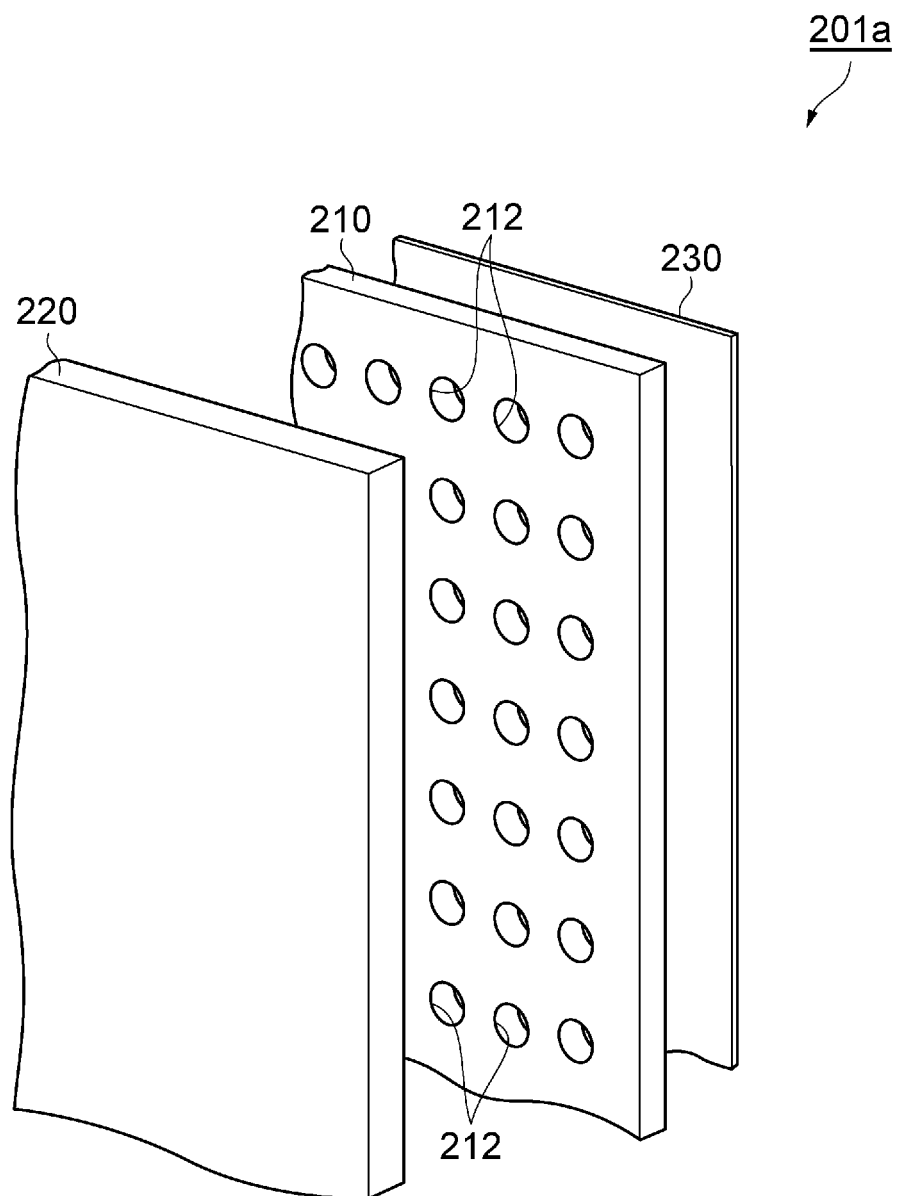
[図16]



[図17]



[図18]



[図19]

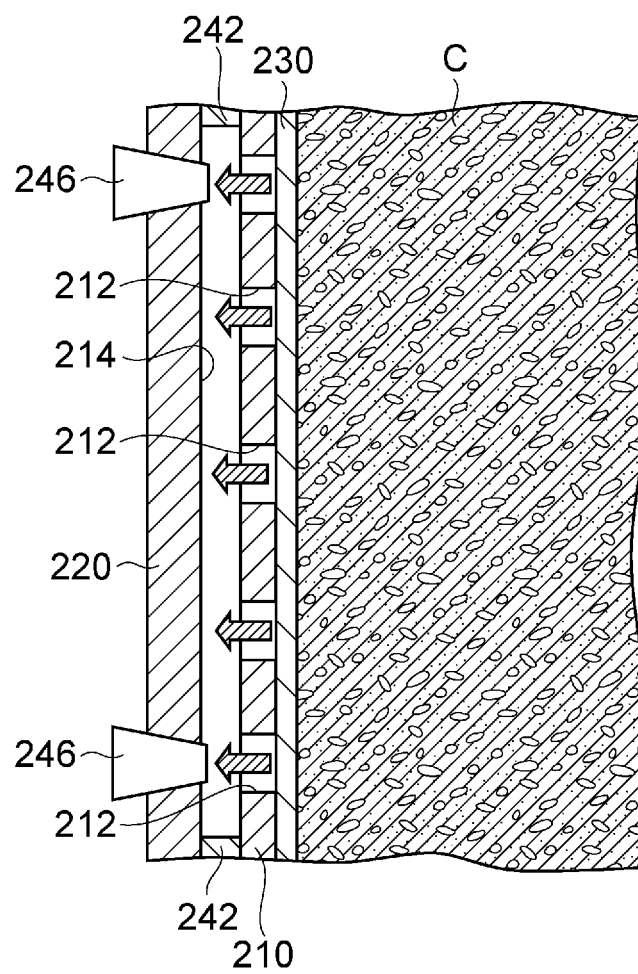
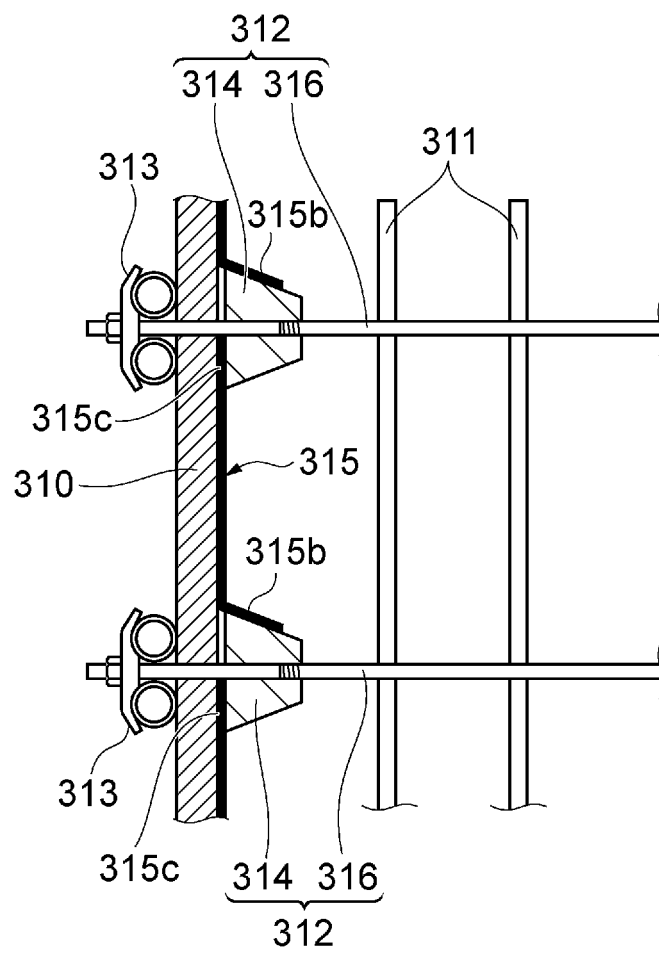
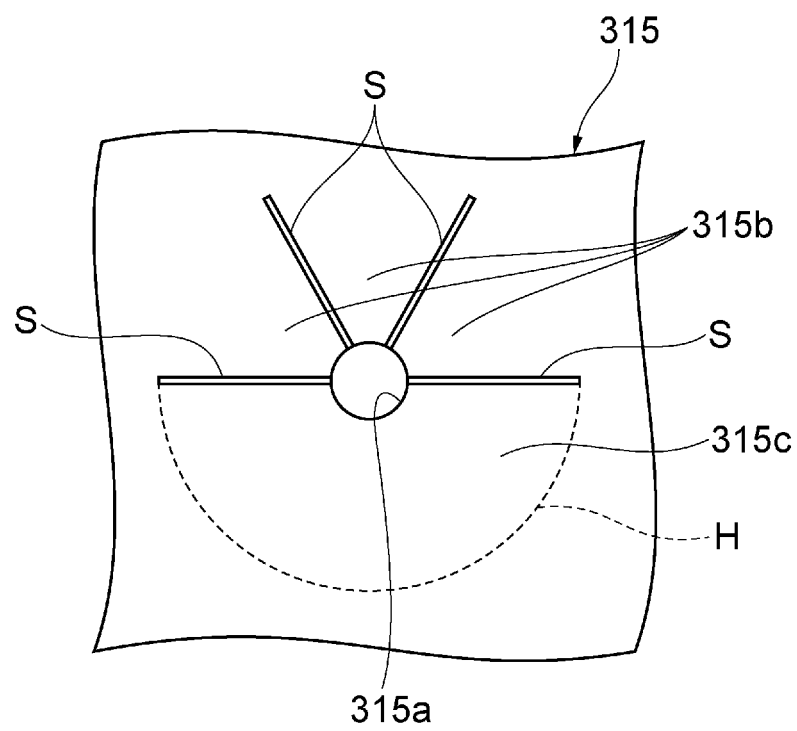


Figure 1 consists of two views of a substrate assembly. The left view is a cross-sectional side view showing a central substrate 210 with a top surface 242 and a bottom surface 242. The substrate 210 is composed of alternating layers 212 and 214. A layer 220 is located between the bottom surface 242 and the bottom layer 212. Two wedge-shaped components 246 are positioned on the top and bottom surfaces of the substrate 210. Arrows point to the left from the top and bottom surfaces. The right view is a top-down view of the substrate 210, showing a rectangular shape with a wavy top edge. The surface is filled with a pattern of diagonal lines and small, irregular shapes. A label 'C' is located in the upper right corner, and a label '230' is located in the upper left corner.

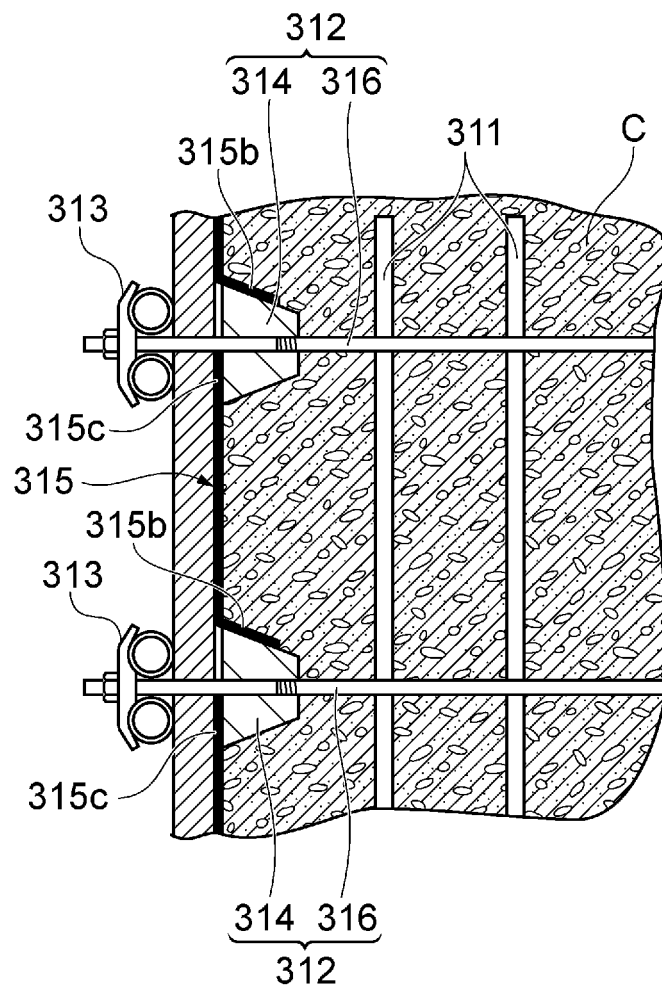
[図21]



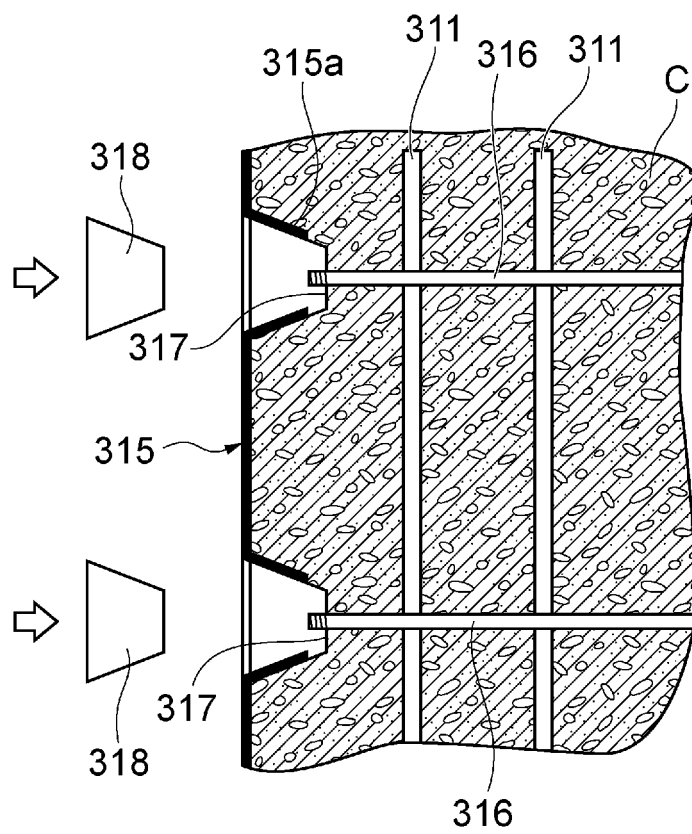
[図22]



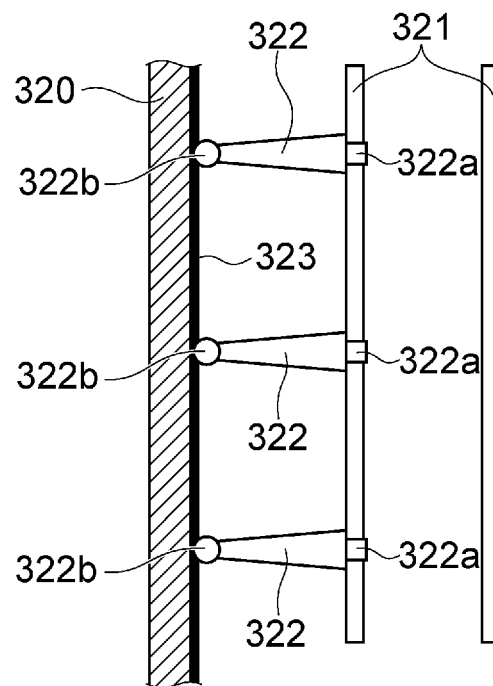
[図23]



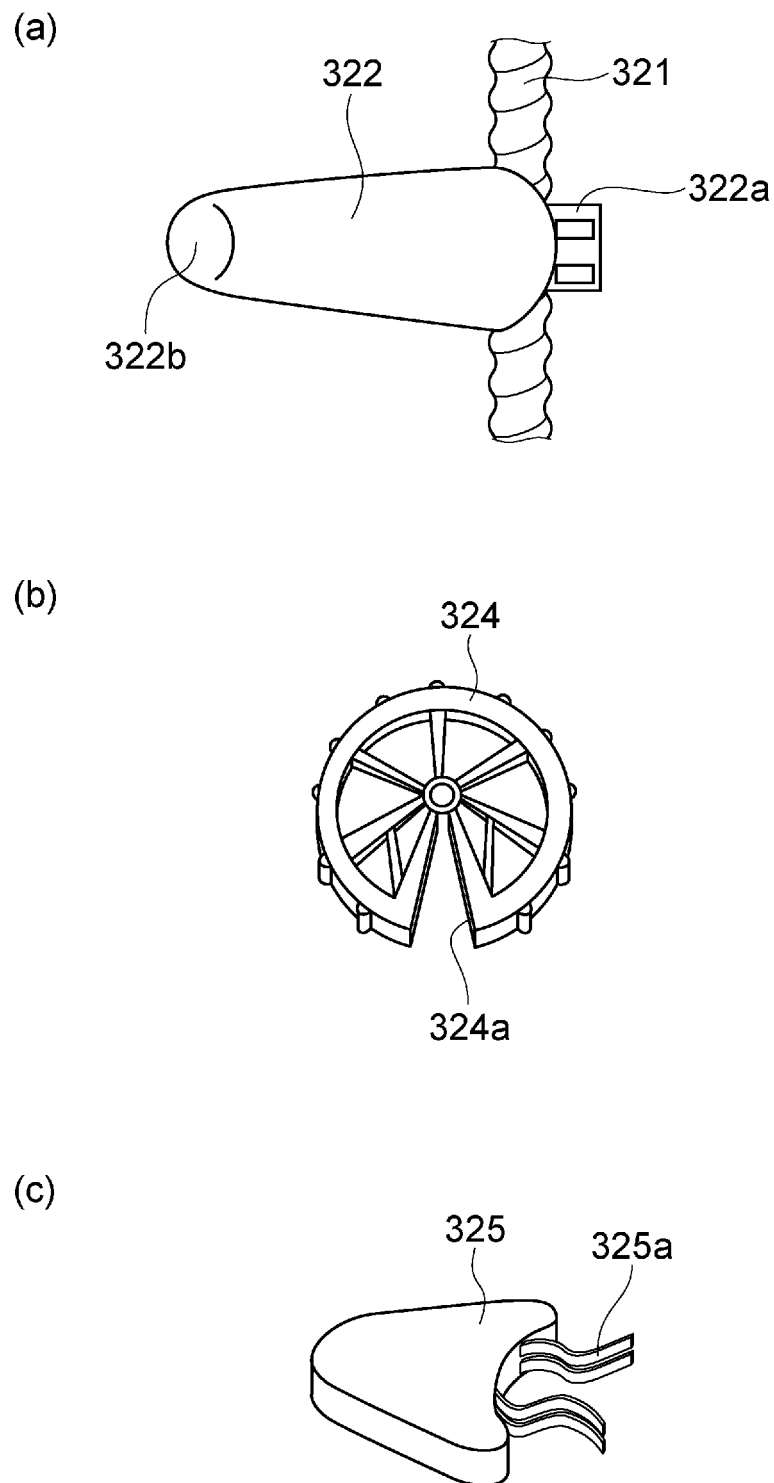
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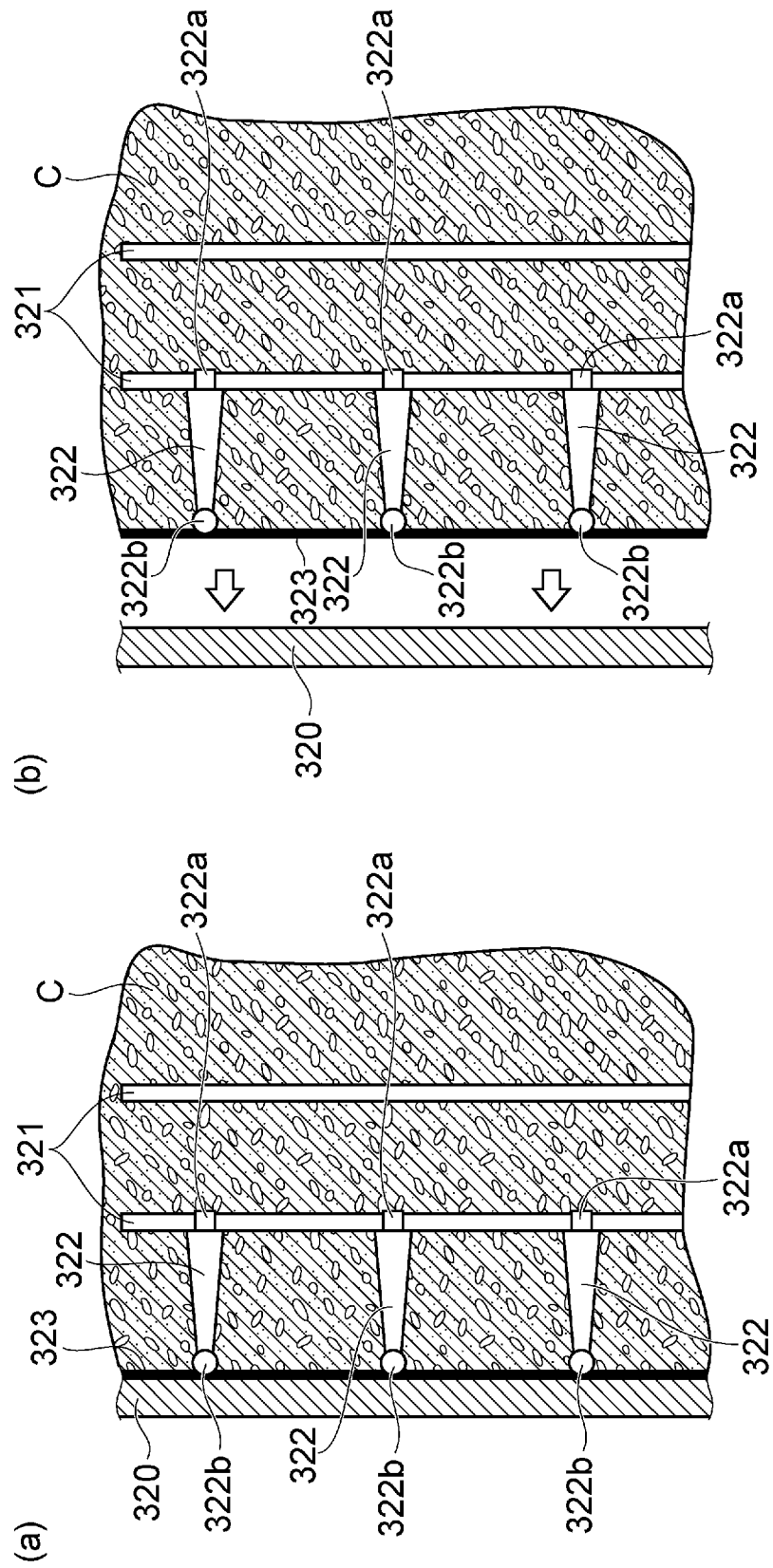
[図26]



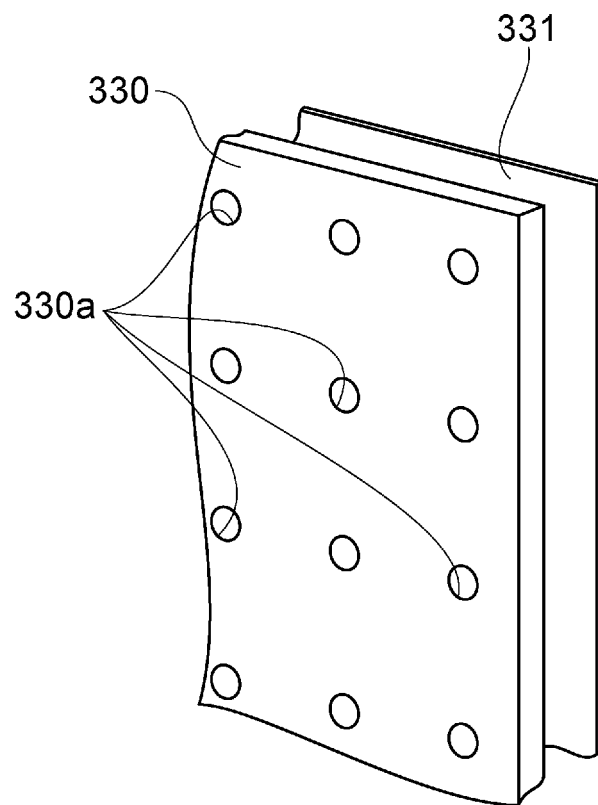
[図27]



[図28]



[図29]



[図30]

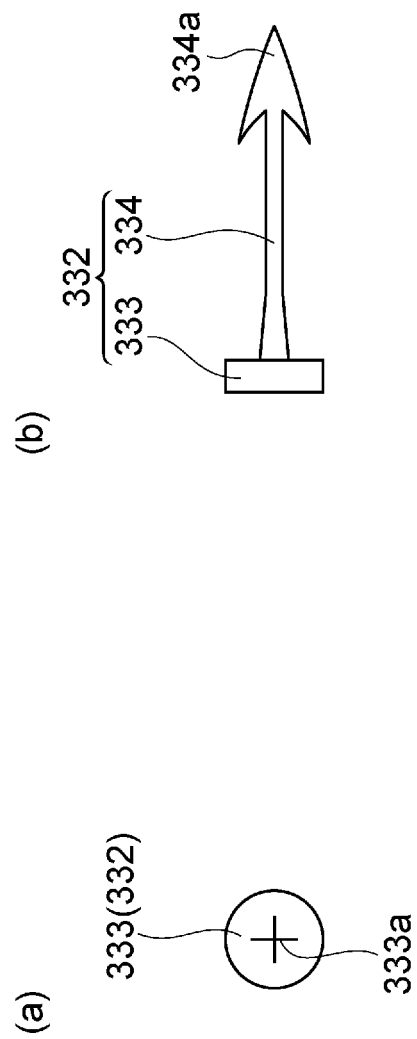
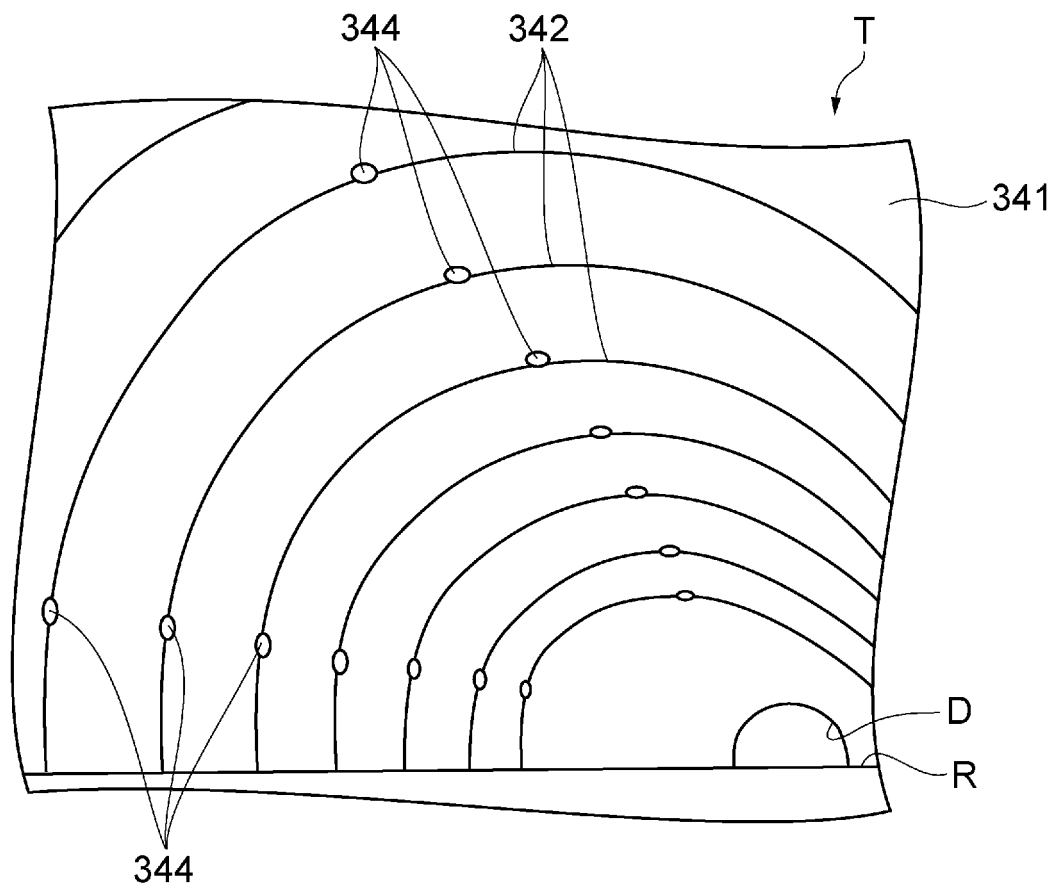


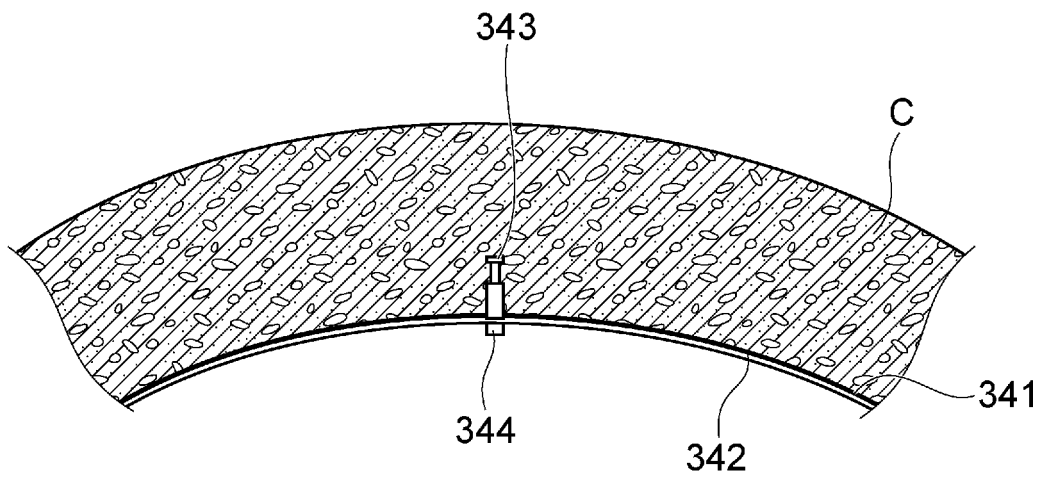
Figure 1 consists of three cross-sectional views of a semiconductor device, labeled (a), (b), and (c), showing the progression of a manufacturing process.

- (a)** Shows a substrate 330 with a central opening. A layer 331 is formed on the substrate. A patterned layer 332 is formed on top of 331, with a central opening. A layer 333 is formed in the central opening of 332. A layer 334 is formed on top of 331, surrounding the central opening of 332. A layer 334a is formed on top of 334, surrounding the central opening of 332.
- (b)** Shows the device after a layer 331a has been formed on top of 331, surrounding the central opening of 332. The layer 331a is formed on top of 331, surrounding the central opening of 332.
- (c)** Shows the device after a layer 331b has been formed on top of 331, surrounding the central opening of 332. The layer 331b is formed on top of 331, surrounding the central opening of 332.

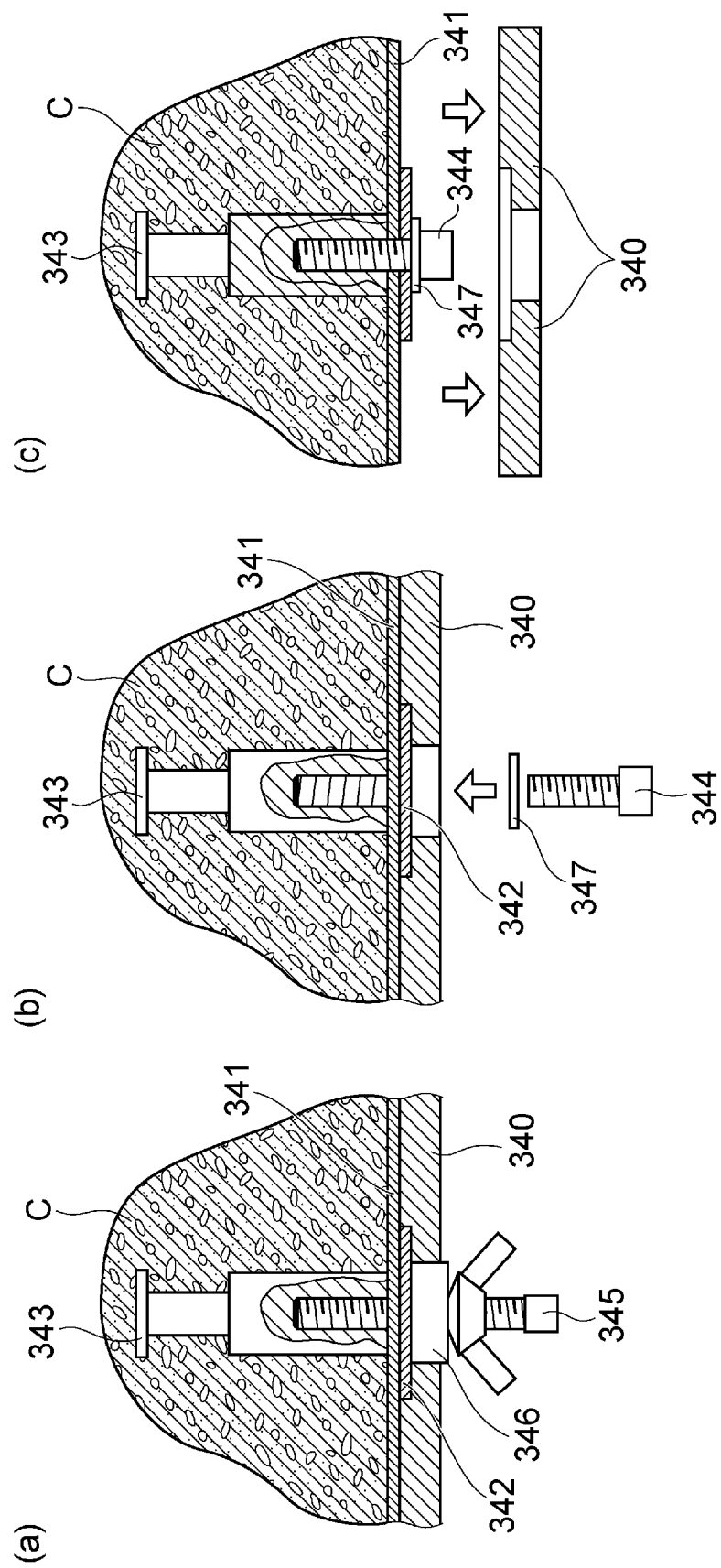
[図32]



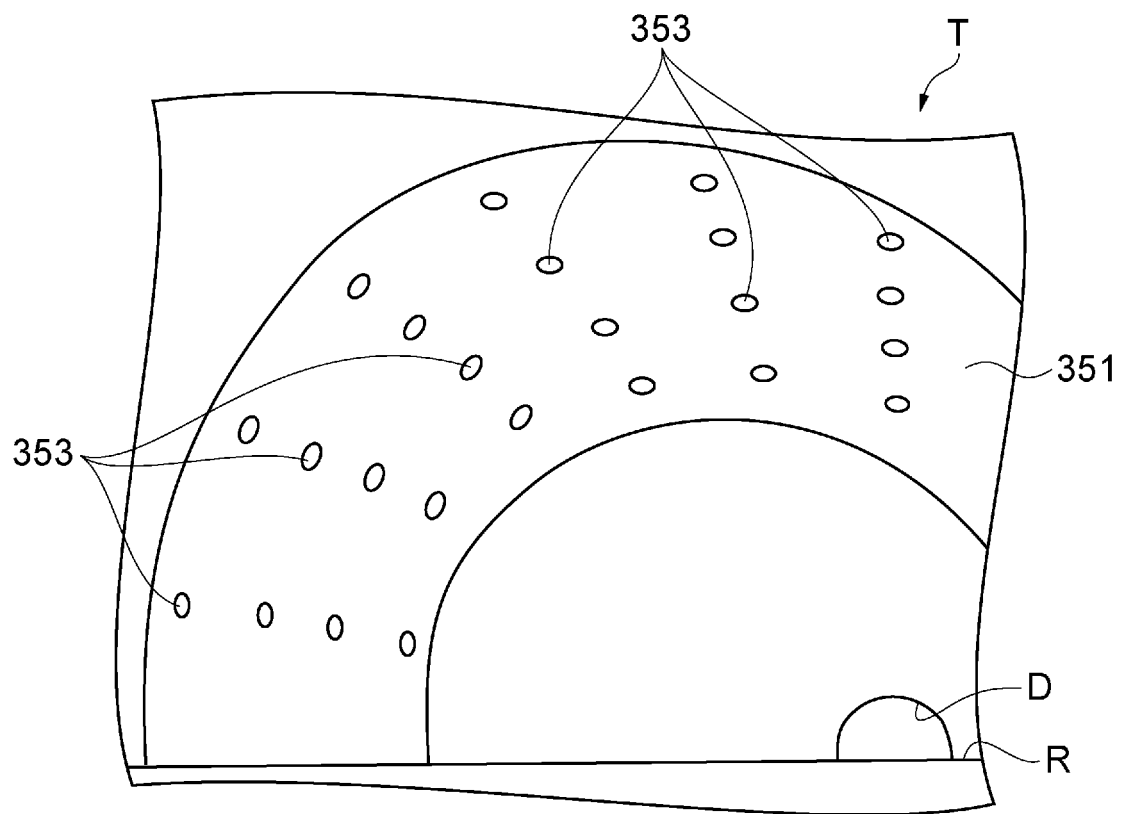
[図33]



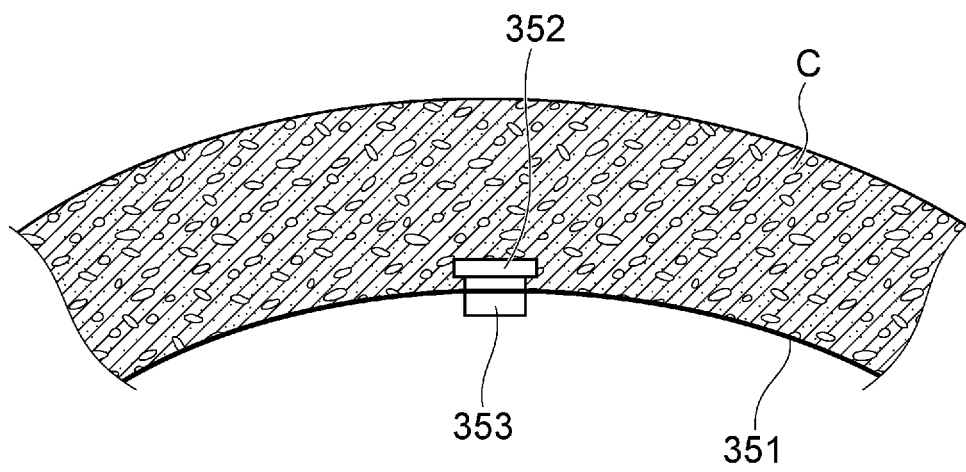
[図34]



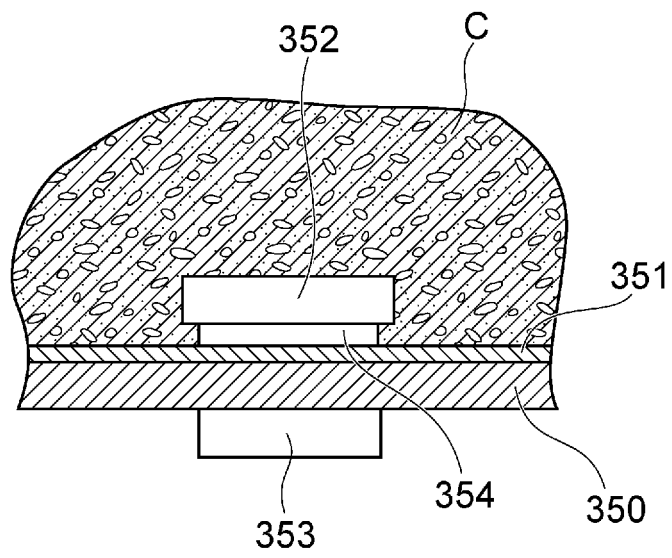
[図35]



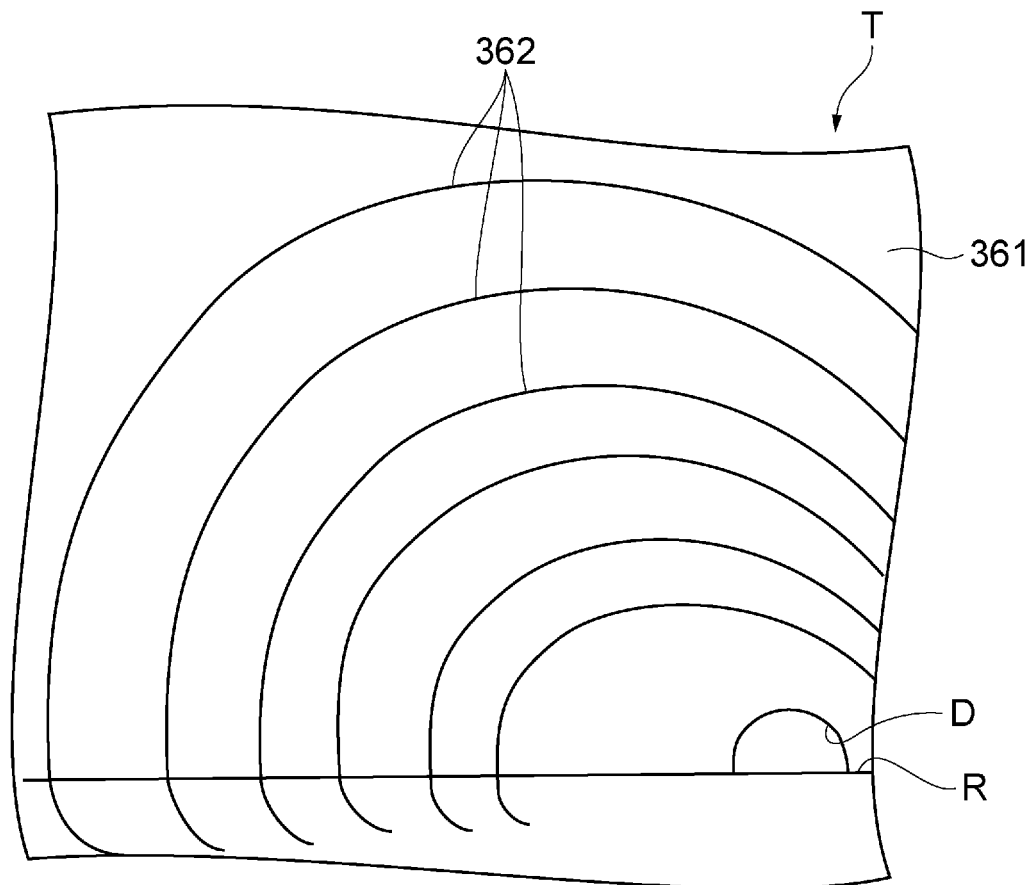
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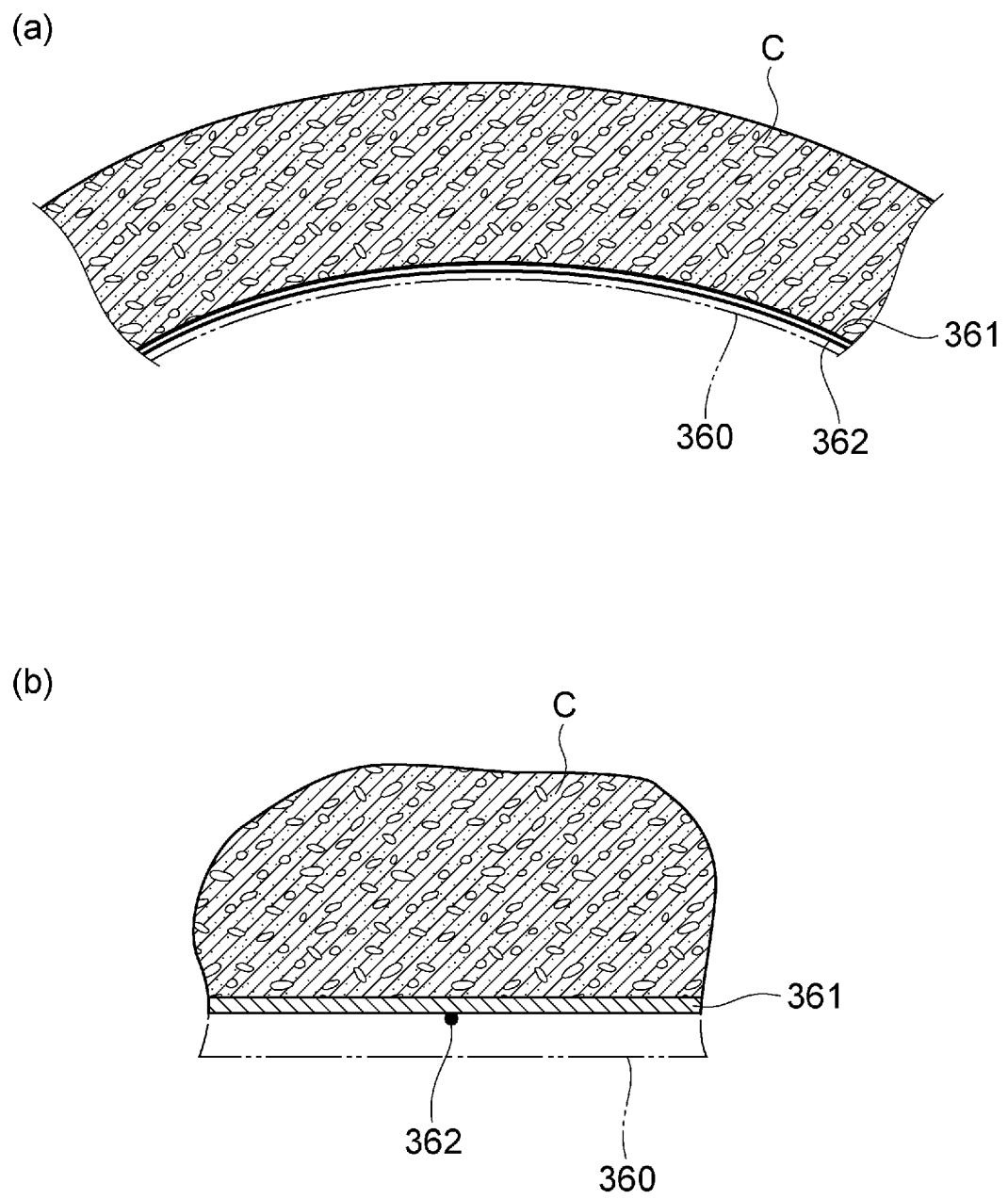
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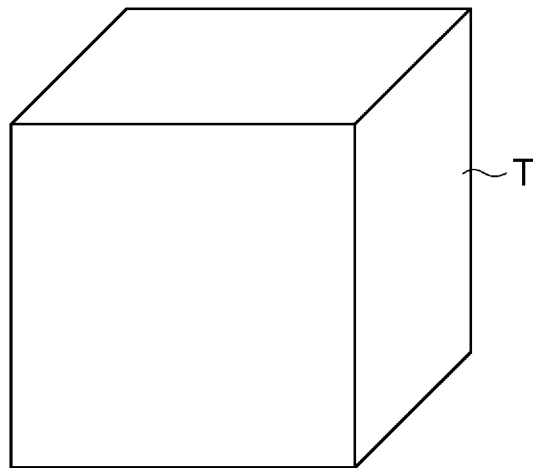
[図38]



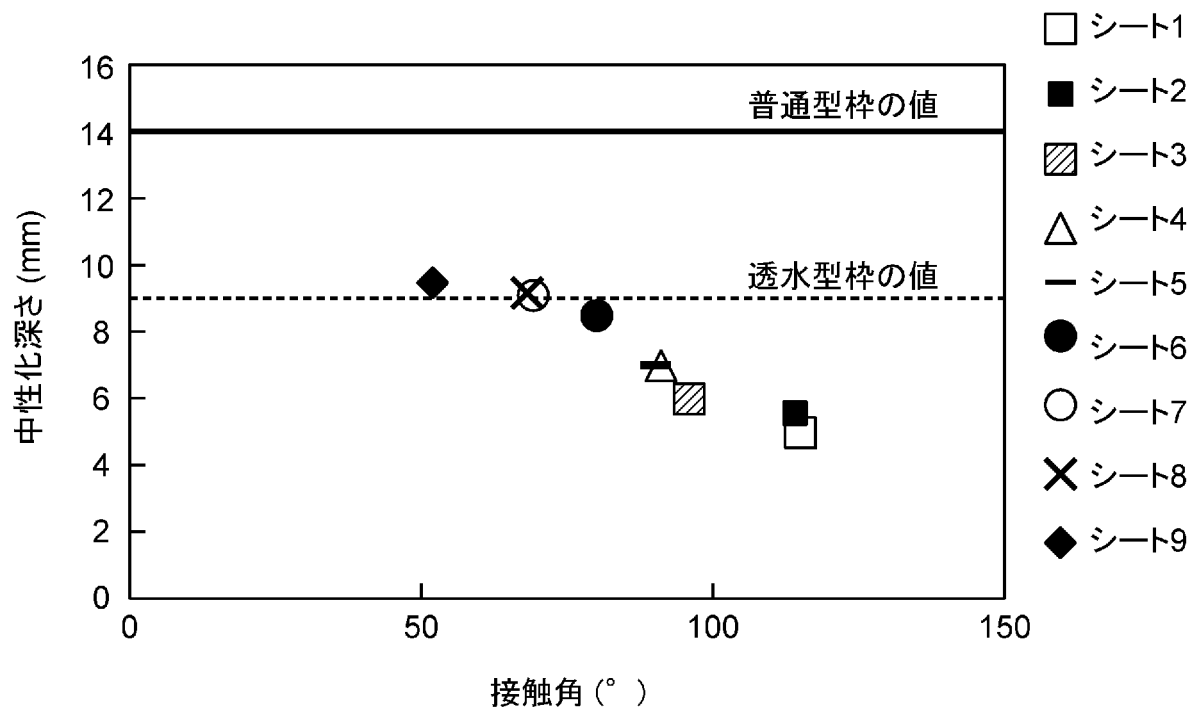
[図39]



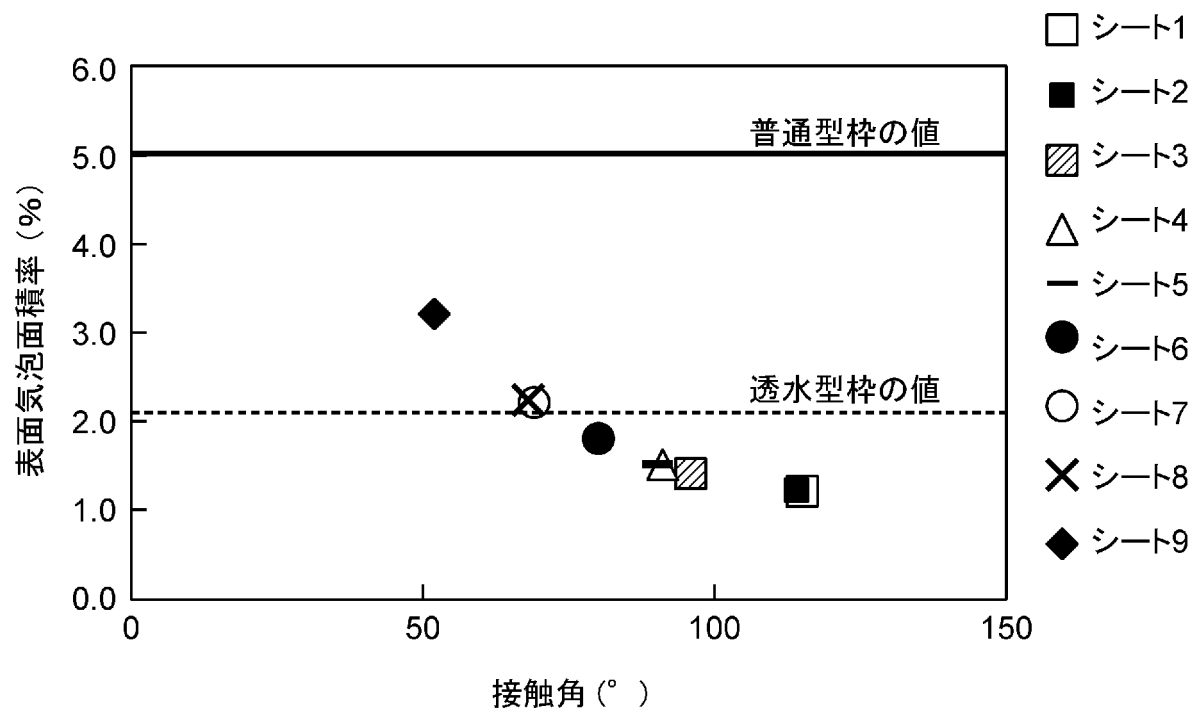
[図40]



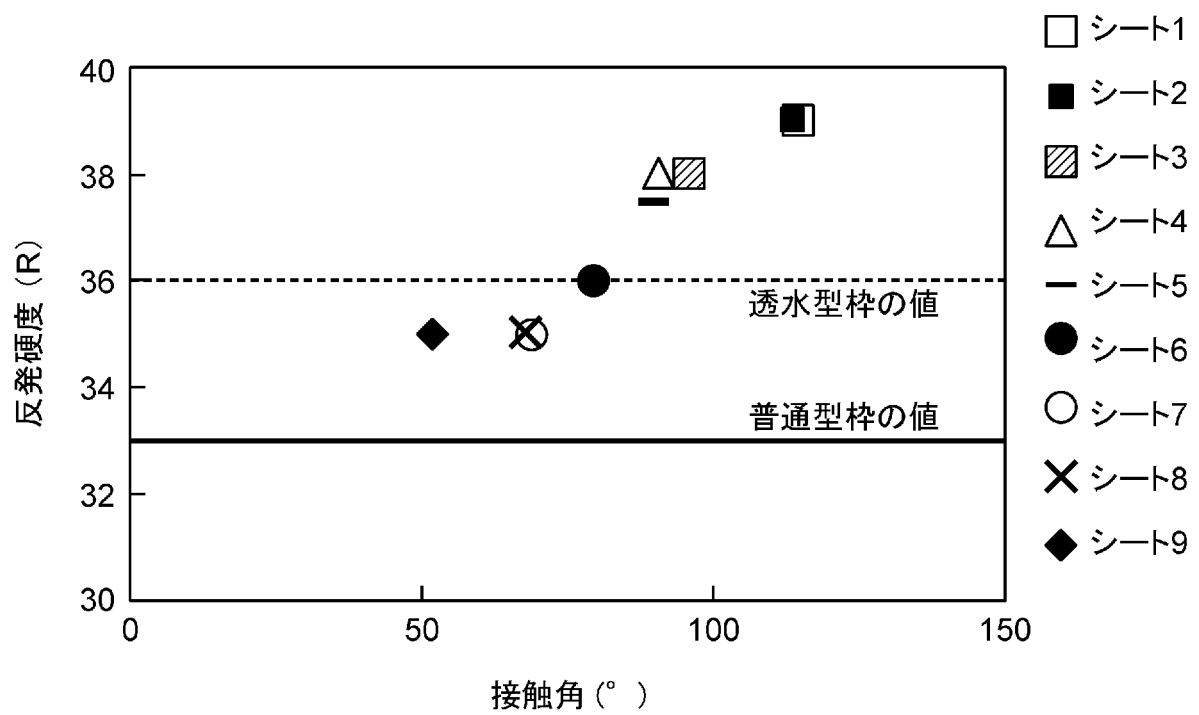
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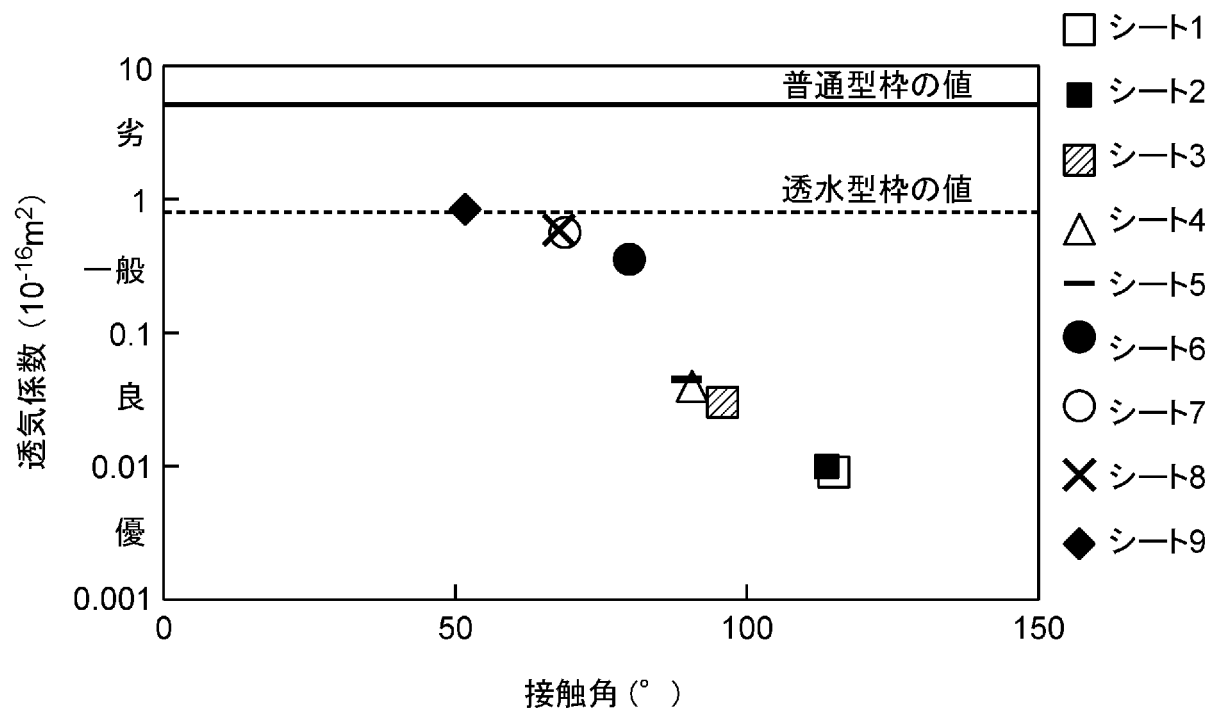
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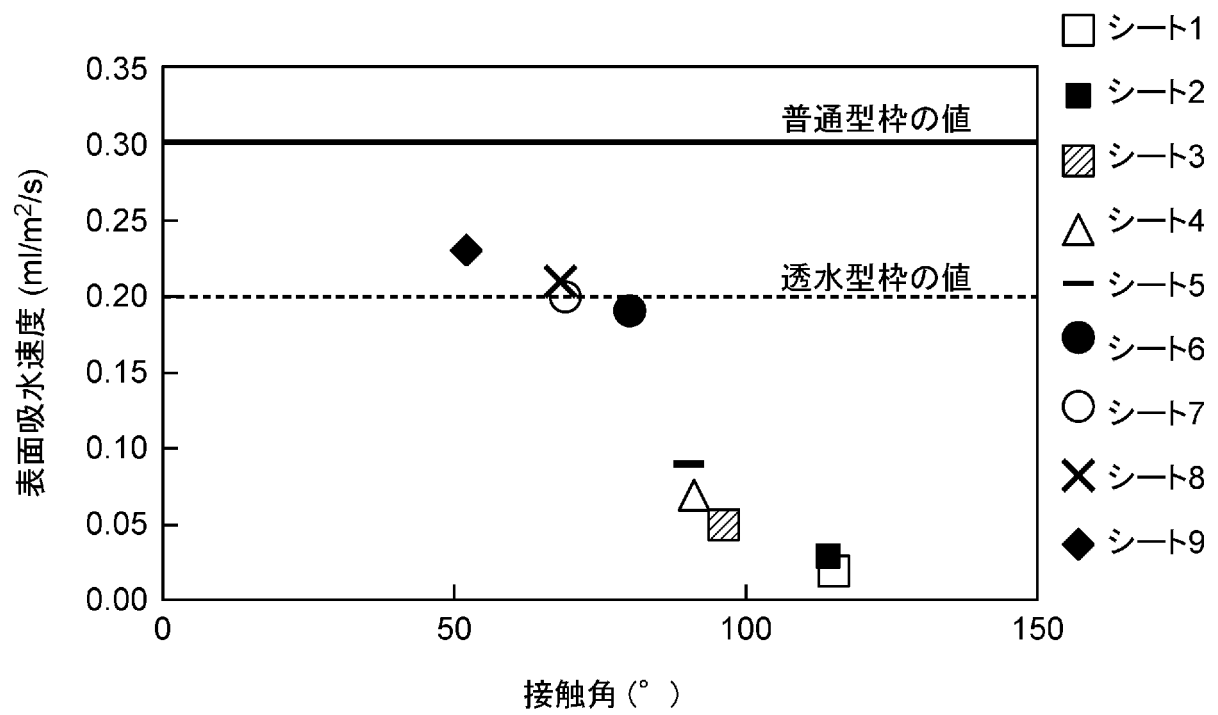
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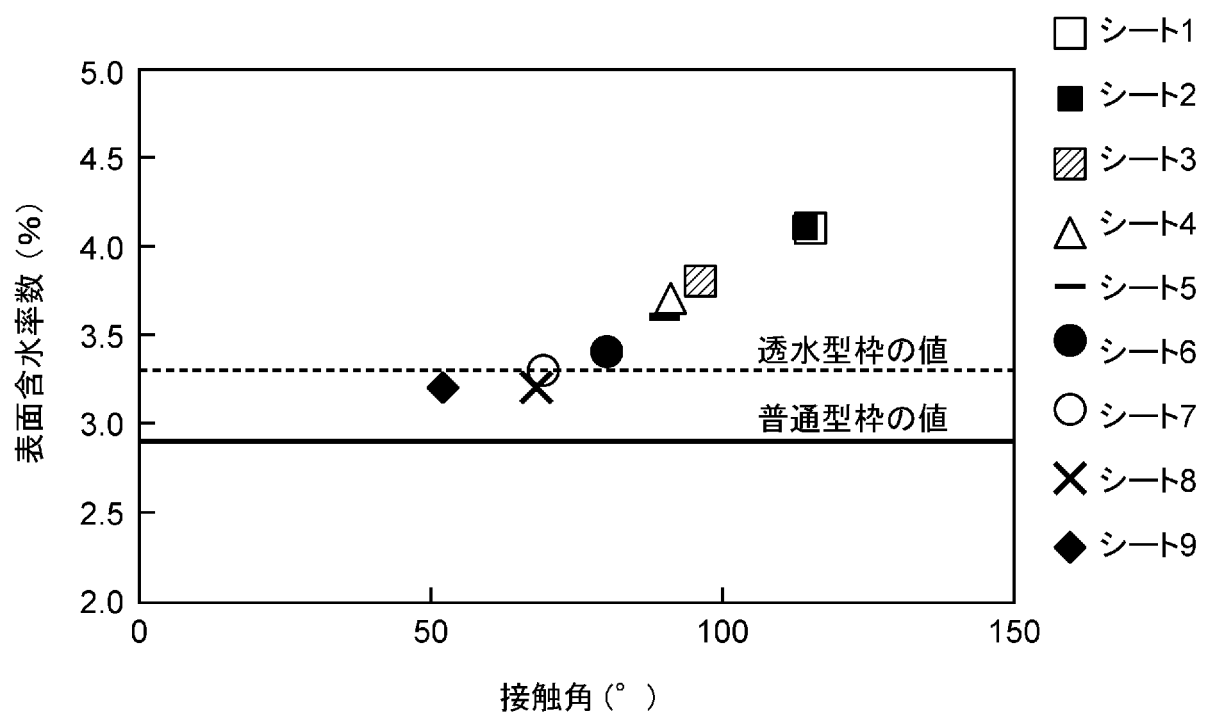
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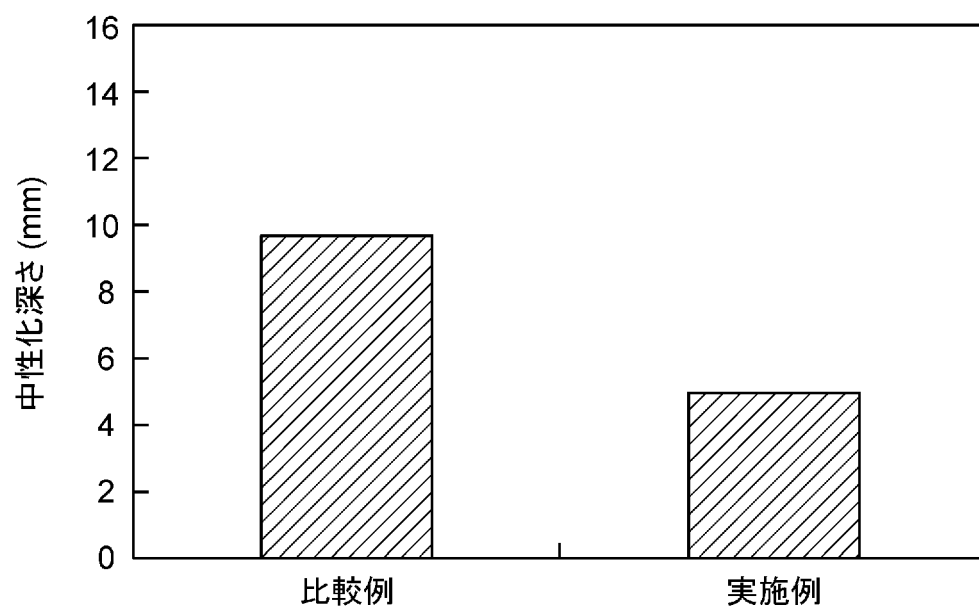
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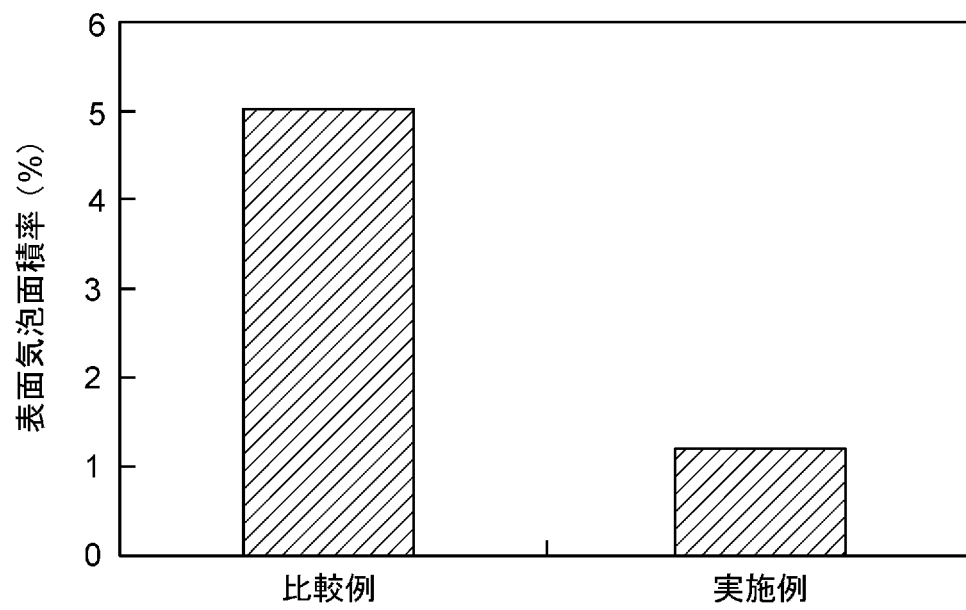
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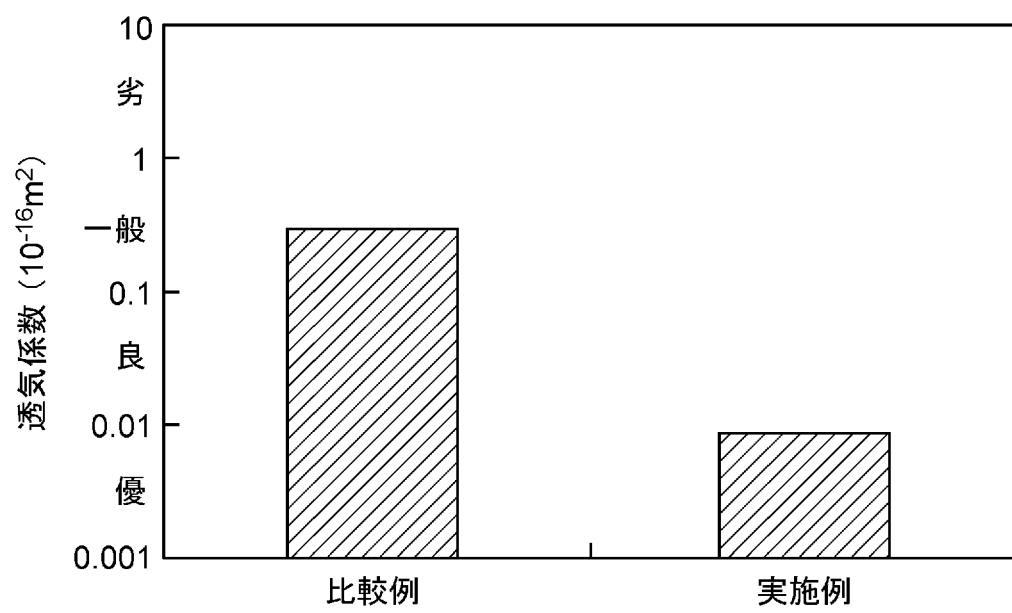
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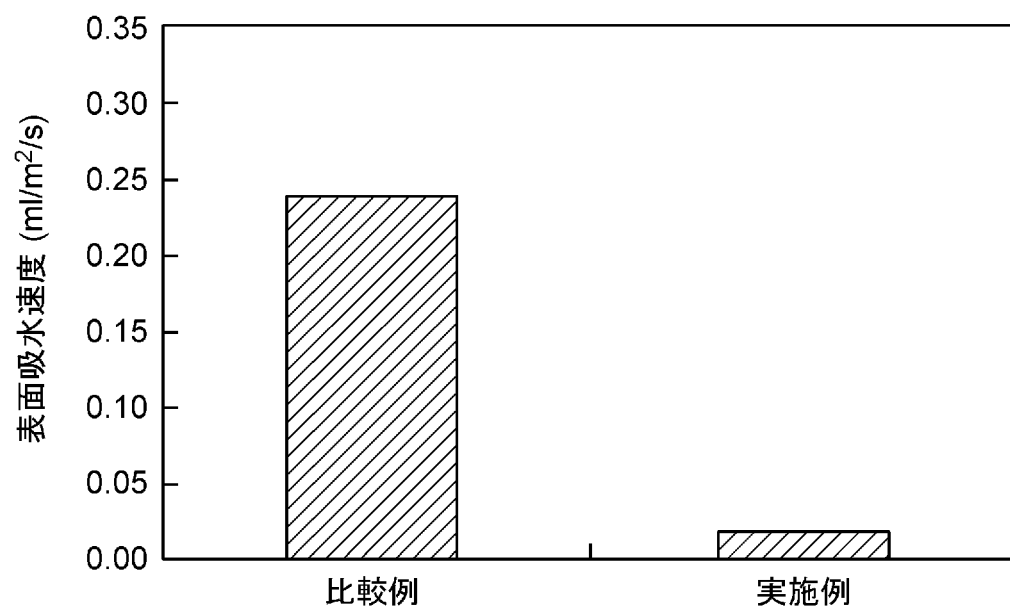
[図48]



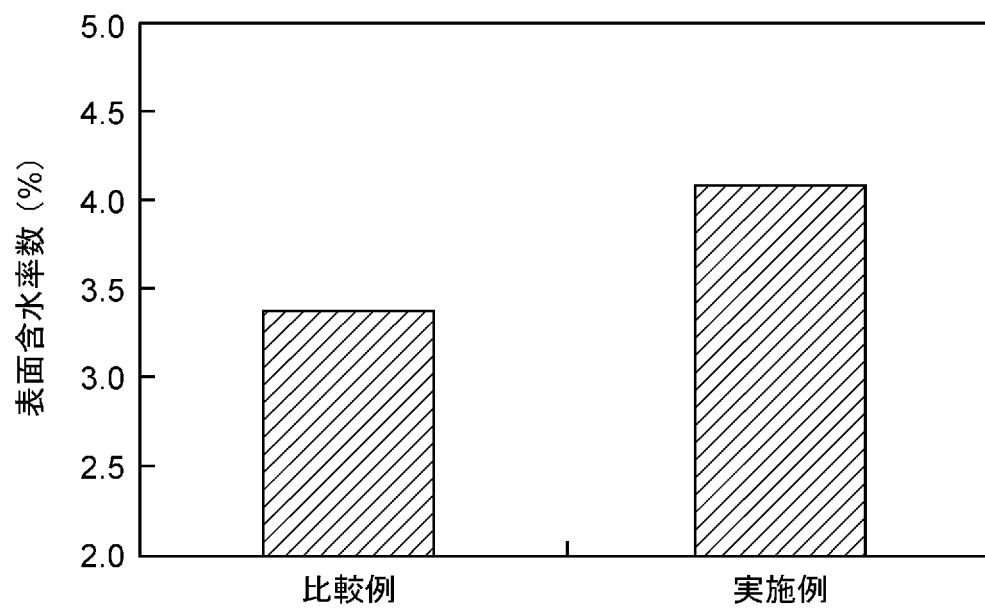
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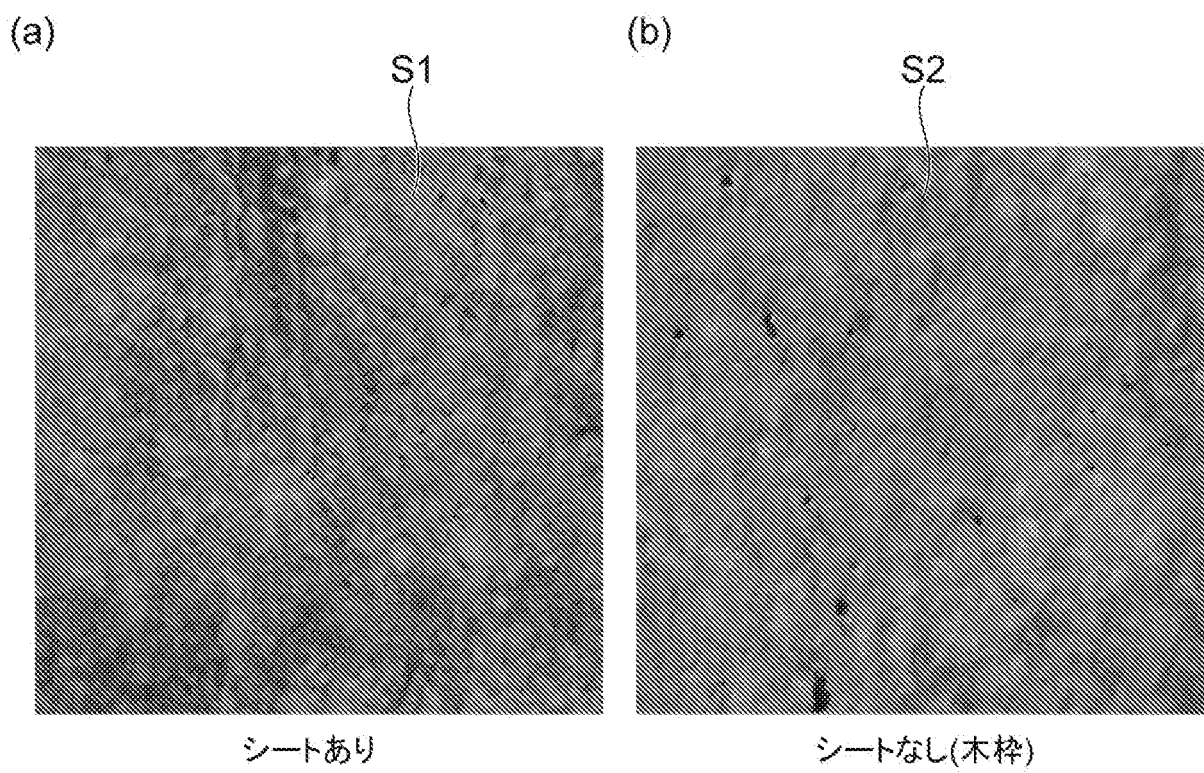
[図50]



[図51]



[図52]



[図53]

